Noritaka Usami

List of Publications by Year
in descending order

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587	9,732	50276	74163
papers	citations	46 h-index	75 g-index

589	589	589	4576
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Silicon Nanocrystals Embedded in Nanolayered Silicon Oxide for Crystalline Silicon Solar Cells. ACS Applied Nano Materials, 2022, 5, 1820-1827.	5.0	11
2	Fractal dimension analogous scale-invariant derivative of Hirschâ€™s index. Applied Network Science, 2022, 7, .	1.5	0
3	Effects of grain boundary structure and shape of the solidâ€“liquid interface on the growth direction of the grain boundaries in multicrystalline silicon. CrystEngComm, 2022, 24, 1948-1954.	2.6	4
4	Zn_{1â€“x}Ge_xO_y Passivating Interlayers for BaSi₂ Thin-Film Solar Cells. ACS Applied Materials & Interfaces, 2022, 14, 13828-13835.	8.0	10
5	Fabrication of BaSi₂ homojunction diodes on Nb-doped TiO₂ coated glass substrates by aluminum-induced crystallization and two-step evaporation method. Japanese Journal of Applied Physics, 2022, 61, SC1029.	1.5	2
6	Data-Driven Optimization and Experimental Validation for the Lab-Scale Mono-Like Silicon Ingot Growth by Directional Solidification. ACS Omega, 2022, 7, 6665-6673.	3.5	10
7	Improved conversion efficiency of p-type BaSi₂/n-type crystalline Si heterojunction solar cells by a low growth rate deposition of BaSi₂. AIP Advances, 2022, 12, 045115.	1.3	13
8	Study on electrical activity of grain boundaries in silicon through systematic control of structural parameters and characterization using a pretrained machine learning model. Journal of Applied Physics, 2022, 132, .	2.5	3
9	Activation energy of hydrogen desorption from high-performance titanium oxide carrier-selective contacts with silicon oxide interlayers. Current Applied Physics, 2021, 21, 36-42.	2.4	12
10	Propagation of Crystal Defects during Directional Solidification of Silicon via Induction of Functional Defects. Crystals, 2021, 11, 90.	2.2	5
11	Passivation mechanism of the high-performance titanium oxide carrier-selective contacts on crystalline silicon studied by spectroscopic ellipsometry. Japanese Journal of Applied Physics, 2021, 60, SBBF04.	1.5	6
12	Simulation study on lateral minority carrier transport in the surface inversion layer of the p-aSi:H/i-aSi:H/cSi heterojunction solar cell. Japanese Journal of Applied Physics, 2021, 60, 026503.	1.5	2
13	Mechanisms of carrier lifetime enhancement and conductivity-type switching on hydrogen-incorporated arsenic-doped BaSi2. Thin Solid Films, 2021, 724, 138629.	1.8	8
14	(Invited) Application of Machine Learning for High-Performance Multicrystalline Materials. ECS Transactions, 2021, 102, 11-16.	0.5	0
15	Occurrence Prediction of Dislocation Regions in Photoluminescence Image of Multicrystalline Silicon Wafers Using Transfer Learning of Convolutional Neural Network. IEICE Transactions on Fundamentals of Electronics, Communications and Computer Sciences, 2021, E104.A, 857-865.	0.3	1
16	Realization of the Crystalline Silicon Solar Cell Using Nanocrystalline Transport Path in Ultra-thin Dielectrics for Reinforced Passivating Contact. , 2021, , .		0
17	Fabrication of Silicon Nanowire Metal-Oxide-Semiconductor Capacitors with Al2O3/TiO2/Al2O3 Stacked Dielectric Films for the Application to Energy Storage Devices. Energies, 2021, 14, 4538.	3.1	7
18	Direct prediction of electrical properties of grain boundaries from photoluminescence profiles using machine learning. Applied Physics Letters, 2021, 119, .	3.3	2

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19	Improved Performance of Titanium Oxide/Silicon Oxide Electronâ€Selective Contacts by Implementation of Magnesium Interlayers. Physica Status Solidi (A) Applications and Materials Science, 2021, 218, 2100296.	1.8	3
20	Contact control of Al/Si interface of Si solar cells by local contact opening method. Materials Chemistry and Physics, 2021, 270, 124833.	4.0	1
21	Application of Bayesian optimization for high-performance TiO /SiO /c-Si passivating contact. Solar Energy Materials and Solar Cells, 2021, 230, 111251.	6.2	7
22	Fabrication of heterojunction crystalline Si solar cells with BaSi₂ thin films prepared by a two-step evaporation method. Japanese Journal of Applied Physics, 2021, 60, 105503.	1.5	12
23	Impact of chemically grown silicon oxide interlayers on the hydrogen distribution at hydrogenated amorphous silicon/crystalline silicon heterointerfaces. Applied Surface Science, 2021, 567, 150799.	6.1	6
24	Versatile fabrication of a passivation material, solute PEDOT:PSS, for a c-Si substrate using alcoholic solvents. Sustainable Energy and Fuels, 2021, 5, 666-670.	4.9	0
25	Application of Bayesian optimization for improved passivation performance in TiO_x/SiO_y/c-Si heterostructure by hydrogen plasma treatment. Applied Physics Express, 2021, 14, 025503.	2.4	15
26	Origin of recombination activity of non-coherent Î£3{111} grain boundaries with a positive deviation in the tilt angle in cast-grown silicon ingots. Applied Physics Express, 2021, 14, 011002.	2.4	7
27	Surface-orientation control of silicon thin films via aluminum-induced crystallization on monocrystalline cubic substrates. Journal of Crystal Growth, 2020, 533, 125441.	1.5	2
28	The impact of highly excessive PbI₂ on the correlation of MAPbI₃ perovskite morphology and carrier lifetimes. Journal of Materials Chemistry C, 2020, 8, 14481-14489.	5.5	7
29	Determination of carrier recombination velocity at inclined grain boundaries in multicrystalline silicon through photoluminescence imaging and carrier simulation. Journal of Applied Physics, 2020, 128, 125103.	2.5	8
30	Reactive deposition growth of highly (001)-oriented BaSi2 films by close-spaced evaporation. Materials Science in Semiconductor Processing, 2020, 113, 105044.	4.0	17
31	Influence of the time-dependent vapor composition on structural properties of the BaSi₂ thin films fabricated by vacuum evaporation. Japanese Journal of Applied Physics, 2020, 59, SFFA10.	1.5	11
32	Impact of Ge deposition temperature on parameters of c-Si solar cells with surface texture formed by etching of Si using SiGe islands as a mask. Materials Science in Semiconductor Processing, 2020, 114, 105065.	4.0	5
33	Drastic enhancement of photoresponsivity in C-doped BaSi2 films formed by radio-frequency sputtering. Japanese Journal of Applied Physics, 2020, 59, SFFA06.	1.5	6
34	Effects of evaporation vapor composition and post-annealing conditions on carrier density of undoped BaSi₂ evaporated films. Japanese Journal of Applied Physics, 2020, 59, SFFA05.	1.5	13
35	Impact of deposition of indium tin oxide double layers on hydrogenated amorphous silicon/crystalline silicon heterojunction. AIP Advances, 2020, 10, 065008.	1.3	7
36	Significant enhancement of photoresponsivity in As-doped n-BaSi₂epitaxial films by atomic hydrogen passivation. Applied Physics Express, 2020, 13, 051001.	2.4	8

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37	Atomic hydrogen passivation for photoresponsivity enhancement of boron-doped p-BaSi2 films and performance improvement of boron-doped p-BaSi2/n-Si heterojunction solar cells. Journal of Applied Physics, 2020, 127, .	2.5	13
38	Effect of forming gas annealing on hydrogen content and surface morphology of titanium oxide coated crystalline silicon heterocontacts. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2020, 38, 022415.	2.1	5
39	Scalable fabrication of GaN on amorphous substrates via MOCVD on highly oriented silicon seed layers. Journal of Crystal Growth, 2020, 535, 125522.	1.5	2
40	Point defects in BaSi2 thin films for photovoltaic applications studied by positron annihilation spectroscopy. Journal of Applied Physics, 2020, 127, .	2.5	7
41	Effect of hydrogen plasma treatment on the passivation performance of TiOx on crystalline silicon prepared by atomic layer deposition. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2020, 38, .	2.1	15
42	Synthesis of Mg₂Si thin film by thermal treatment under inert gas atmosphere and evaluation of film quality. Japanese Journal of Applied Physics, 2020, 59, SFFB03.	1.5	1
43	Preparation and thermoelectric characterization of phosphorus-doped Si nanocrystals/silicon oxide multilayers. Japanese Journal of Applied Physics, 2020, 59, SGGF09.	1.5	1
44	Fabrication of group IV semiconductor alloys on Si substrate applying Al paste with screen-printing. Japanese Journal of Applied Physics, 2020, 59, SGGF07.	1.5	0
45	3D visualization of growth interfaces in cast Si ingot using inclusions distribution. Journal of Crystal Growth, 2020, 535, 125535.	1.5	0
46	Undoped p-type BaSi₂ emitter prepared by thermal evaporation and post-annealing for crystalline silicon heterojunction solar cells. Applied Physics Express, 2020, 13, 051002.	2.4	10
47	Effect of Si substrate modification on improving the crystalline quality, optical and electrical properties of thermally-evaporated BaSi2 thin-films for solar cell applications. International Journal of Modern Physics B, 2020, 34, 2050068.	2.0	1
48	(Invited) Engineering Strain, Defects, and Electronic Properties of (110)-Oriented Strained Si. ECS Transactions, 2020, 98, 277-290.	0.5	3
49	Effect of the Niobium-Doped Titanium Oxide Thickness and Thermal Oxide Layer for Silicon Quantum Dot Solar Cells as a Dopant-Blocking Layer. Nanoscale Research Letters, 2020, 15, 39.	5.7	6
50	Surface inversion layer effective minority carrier mobility as one of the measures of surface quality of the p-aSi:H/i-aSi:H/cSi heterojunction solar cell. Japanese Journal of Applied Physics, 2020, 59, SGGF06.	1.5	1
51	Generation of dislocation clusters at triple junctions of random angle grain boundaries during cast growth of silicon ingots. Applied Physics Express, 2020, 13, 105505.	2.4	8
52	Work function of indium oxide thin films on p-type hydrogenated amorphous silicon. , 2020, , .		0
53	Structural properties of triple junctions acting as dislocation sources in high-performance Si ingots. , 2020, , .		0
54	Fabrication of silicon-nanocrystals-embedded silicon oxide passivating contacts. , 2020, , .		0

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55	3D visualization and analysis of dislocation clusters in multicrystalline silicon ingot by approach of data science. Solar Energy Materials and Solar Cells, 2019, 189, 239-244.	6.2	15
56	Hydrogen concentration at a-Si:H/c-Si heterointerfacesâ€"The impact of deposition temperature on passivation performance. AIP Advances, 2019, 9, .	1.3	27
57	Tuning the Electrical Properties of Titanium Oxide Bilayers Prepared by Atomic Layer Deposition at Different Temperatures. Physica Status Solidi (A) Applications and Materials Science, 2019, 216, 1900495.	1.8	6
58	Application of artificial neural network to optimize sensor positions for accurate monitoring: an example with thermocouples in a crystal growth furnace. Applied Physics Express, 2019, 12, 125503.	2.4	14
59	MÃ¶ssbauer spectroscopic microscope study on diffusion and segregation of Fe impurities in mc-Si wafer. Hyperfine Interactions, 2019, 240, 1.	0.5	1
60	Fine line Al printing on narrow point contact opening for front side metallization. AIP Conference Proceedings, 2019, , .	0.4	10
61	Impact of size distributions of Ge islands as etching masks for anisotropic etching on formation of anti-reflection structures. Japanese Journal of Applied Physics, 2019, 58, 045505.	1.5	9
62	Pole figure analysis from electron backscatter diffractionâ€"an effective method of evaluating fiber-textured silicon thin films as seed layers for epitaxy. Applied Physics Express, 2019, 12, 025501.	2.4	1
63	Fabrication of Si1-xGex layer on Si substrate by Screen-Printing. MRS Advances, 2019, 4, 749-754.	0.9	7
64	Effects of Surface Doping of Si Absorbers on the Band Alignment and Electrical Performance of TiO2-Based Electron-Selective Contacts. MRS Advances, 2019, 4, 769-775.	0.9	1
65	Evidence of solute PEDOT:PSS as an efficient passivation material for fabrication of hybrid c-Si solar cells. Sustainable Energy and Fuels, 2019, 3, 1448-1454.	4.9	12
66	Epitaxial growth of SiGe on Si substrate by printing and firing of Alâ€"Ge mixed paste. Japanese Journal of Applied Physics, 2019, 58, 045504.	1.5	5
67	Significant improvement on electrical properties of BaSi2 due to atomic H passivation by radio-frequency plasma. , 2019, , .		0
68	Fabrication of Si1-xSnx Layer on Si Substrate by Screen-Printing of Al-Sn Paste. ECS Transactions, 2019, 93, 61-62.	0.5	0
69	Local Structure of High Performance TiO_x Electronâ€Selective Contact Revealed by Electron Energy Loss Spectroscopy. Advanced Materials Interfaces, 2019, 6, 1801645.	3.7	15
70	Marked enhancement of the photoresponsivity and minority-carrier lifetime of <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:mi>BaS</mml:mi><mml:msub><mml:mi mathvariant="normal">i</mml:mi><mml:mn>2</mml:mn></mml:msub></mml:mrow></mml:math> passivated with atomic hydrogen. Physical Review Materials, 2019, 3, .	2.4	20
71	Electrical properties of TiO TiO_x bilayer prepared by atomic layer deposition at different temperatures. , 2019, , .		0
72	Alternative simple method to realize p-type BaSi2 thin films for Si heterojunction solar cell applications. MRS Advances, 2018, 3, 1435-1442.	0.9	14

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73	Effect of substrate type on the electrical and structural properties of TiO2 thin films deposited by reactive DC sputtering. Journal of Crystal Growth, 2018, 491, 120-125.	1.5	7
74	Fabrication of silicon nanowire based solar cells using TiO2/Al2O3 stack thin films. MRS Advances, 2018, 3, 1419-1426.	0.9	5
75	A quantum-dot spin qubit with coherence limited by charge noise and fidelity higher than 99.9%. Nature Nanotechnology, 2018, 13, 102-106.	31.5	574
76	BaSi₂formation mechanism in thermally evaporated films and its application to reducing oxygen impurity concentration. Japanese Journal of Applied Physics, 2018, 57, 04FS01.	1.5	17
77	Formation of black silicon using SiGe self-assembled islands as a mask for selective anisotropic etching of silicon. Materials Science in Semiconductor Processing, 2018, 75, 143-148.	4.0	11
78	Influence of barrier layerâ€™s height on the performance of Si quantum dot solar cells. Japanese Journal of Applied Physics, 2018, 57, 08RF08.	1.5	3
79	Fabrication of light-trapping structure by selective etching of thin Si substrates masked with a Ge dot layer and nanomasks. Japanese Journal of Applied Physics, 2018, 57, 08RF09.	1.5	7
80	Deposition and Characterization of Si Quantum Dot Multilayers Prepared by Plasma Enhanced Chemical Vapor Deposition using SiH<inf>4</inf> and CO<inf>2</inf> Gases. , 2018, , .		1
81	Local Structure of High Performance TiO<inf>x</inf> Passivating Layer Revealed by Electron Energy Loss Spectroscopy. , 2018, , .		0
82	Evaluation of Si Nanowire MOS Capacitor Using High-k Dielectric Materials. , 2018, , .		1
83	Application of light trapping structure using Ge dot mask by alkaline etching to heterojunction solar cell. , 2018, , .		0
84	Optimized electrical control of a Si/SiGe spin qubit in the presence of an induced frequency shift. Npj Quantum Information, 2018, 4, .	6.7	31
85	Controllable Optical and Electrical Properties of Nb Doped TiO<inf>2</inf> Films by RF Sputtering. , 2018, , .		1
86	Development of the Passivation Layer For P-type CuI Thin Film Fabricated by the 2-step Method as the Novel Hole Selective Contact of Silicon Heterojunction Solar Cells. , 2018, , .		0
87	Improving the photoresponse spectra of BaSi2 layers by capping with hydrogenated amorphous Si layers prepared by radio-frequency hydrogen plasma. AIP Advances, 2018, 8, 055306.	1.3	10
88	Activation mechanism of TiO _x passivating layer on crystalline Si. Applied Physics Express, 2018, 11, 102301.	2.4	14
89	Application of weighted Voronoi diagrams to analyze nucleation sites of multicrystalline silicon ingots. Journal of Crystal Growth, 2018, 499, 62-66.	1.5	4
90	Impact of boron incorporation on properties of silicon solar cells employing p-type polycrystalline silicon grown by aluminum-induced crystallization. Japanese Journal of Applied Physics, 2018, 57, 08RB12.	1.5	3

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91	Investigation of effective near-infrared light-trapping structure with submicron diameter for crystalline silicon thin film solar cells. Japanese Journal of Applied Physics, 2018, 57, 08RB21.	1.5	3
92	Simple method for significant improvement of minority-carrier lifetime of evaporated BaSi 2 thin film by sputtered-AlO x passivation. Materials Science in Semiconductor Processing, 2018, 76, 37-41.	4.0	29
93	Fabrication and properties characterization of BaSi2 thin-films thermally-evaporated on Ge (100) modified substrates. Thin Solid Films, 2018, 663, 14-20.	1.8	2
94	Suppression of Near-interface Oxidation in Thermally-evaporated BaSi2 Films and Its Effects on Preferred Orientation and the Rectification Behavior of n-BaSi2/p+-Si Diodes. MRS Advances, 2018, 3, 1387-1392.	0.9	6
95	Formation of light-trapping structure using Ge islands grown by gas-source molecular beam epitaxy as etching masks. Japanese Journal of Applied Physics, 2018, 57, 08RB04.	1.5	4
96	Study on ion implantation conditions in fabricating compressively strained Si/relaxed Si 1âˆ'x C x heterostructures using the defect control by ion implantation technique. Journal of Crystal Growth, 2017, 468, 601-604.	1.5	0
97	Hole mobility in strained Si/SiGe/vicinal Si(110) grown by gas source MBE. Journal of Crystal Growth, 2017, 468, 625-629.	1.5	8
98	Controlling impurity distributions in crystalline Si for solar cells by using artificial designed defects. Journal of Crystal Growth, 2017, 468, 610-613.	1.5	9
99	Thermal stability of compressively strained Si/relaxed Si 1-x C x heterostructures formed on Ar ion implanted Si (100) substrates. Materials Science in Semiconductor Processing, 2017, 70, 127-132.	4.0	0
100	Exploring the potential of semiconducting BaSi₂for thin-film solar cell applications. Journal Physics D: Applied Physics, 2017, 50, 023001.	2.8	99
101	Investigation of p-type emitter layer materials for heterojunction barium disilicide thin film solar cells. Japanese Journal of Applied Physics, 2017, 56, 05DB04.	1.5	13
102	Effects of grain boundary structure controlled by artificially designed seeds on dislocation generation. Japanese Journal of Applied Physics, 2017, 56, 075501.	1.5	10
103	On the growth mechanism of multicrystalline silicon ingots with small grains fabricated using single-layer silicon beads. Japanese Journal of Applied Physics, 2017, 56, 075502.	1.5	5
104	Boron-doped p-BaSi2/n-Si solar cells formed on textured n-Si(0 0 1) with a pyramid structure consisting of {1 1 1} facets. Journal of Crystal Growth, 2017, 475, 186-191.	1.5	9
105	Effect of ALD-Al2O3 Passivated Silicon Quantum Dot Superlattices on p/i/n+ Solar Cells. IEEE Transactions on Electron Devices, 2017, 64, 2886-2892.	3.0	4
106	Impact of anodic aluminum oxide fabrication and post-deposition anneal on the effective carrier lifetime of vertical silicon nanowires. Solar Energy Materials and Solar Cells, 2017, 166, 39-44.	6.2	2
107	Towards optimized nucleation control in multicrystalline silicon ingot for solar cells. Journal of Crystal Growth, 2017, 468, 620-624.	1.5	6
108	Development of spin-coated copper iodide on silicon for use in hole-selective contacts. Energy Procedia, 2017, 124, 598-603.	1.8	12

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109	Controlling impurity distribution in quasi-mono crystalline Si ingot by seed manipulation for artificially controlled defects technique. Energy Procedia, 2017, 124, 734-739.	1.8	8
110	Growth of strained Si/relaxed SiGe heterostructures on Si(110) substrates using solid-source molecular beam epitaxy. Semiconductor Science and Technology, 2017, 32, 114002.	2.0	7
111	Effects of surface morphology randomness on optical properties of Si-based photonic nanostructures. Japanese Journal of Applied Physics, 2017, 56, 08MA02.	1.5	3
112	Formation of metastable cubic phase in SnS thin films fabricated by thermal evaporation. Thin Solid Films, 2017, 639, 7-11.	1.8	29
113	Selective etching of Si, SiGe, Ge and its usage for increasing the efficiency of silicon solar cells. Semiconductors, 2017, 51, 1542-1546.	0.5	9
114	Postannealing effects on undoped BaSi₂evaporated films grown on Si substrates. Japanese Journal of Applied Physics, 2017, 56, 05DB05.	1.5	25
115	Minority-carrier lifetime and photoresponse properties of B-doped p-BaSi₂, a potential light absorber for solar cells. Japanese Journal of Applied Physics, 2017, 56, 05DB01.	1.5	7
116	Fabrication of BaSi2 thin films capped with amorphous Si using a single evaporation source. Thin Solid Films, 2017, 636, 546-551.	1.8	9
117	Optical characterization of double-side-textured silicon wafer based on photonic nanostructures for thin-wafer crystalline silicon solar cells. Japanese Journal of Applied Physics, 2017, 56, 04CS01.	1.5	1
118	Growth of BaSi₂film on Ge(100) by vacuum evaporation and its photoresponse properties. Japanese Journal of Applied Physics, 2017, 56, 05DB06.	1.5	5
119	Post-annealing effects on the surface structure and carrier lifetime of evaporated BaSi₂ films. Japanese Journal of Applied Physics, 2017, 56, 04CS07.	1.5	9
120	Solar Cells Application of p-type poly-Si Thin Film by Aluminum Induced Crystallization. , 2017, , .		0
121	Numerical simulation and performance optimization of perovskite solar cell. , 2017, , .		2
122	Overview of Surface Passivation Schemes for Thin Film Solar Cells. , 2017, , .		0
123	Fabrication of CuI/a-Si:H/c-Si Structure for Application to Hole-selective Contacts of Heterojunction Si Solar Cells. , 2017, , .		0
124	Investigation on the origin of preferred a -axis orientation of BaSi 2 films deposited on Si(100) by thermal evaporation. Materials Science in Semiconductor Processing, 2017, 72, 93-98.	4.0	13
125	Compressively strained Si/Si1â^'xCxheterostructures formed on Ar ion implanted Si(100) substrates. Japanese Journal of Applied Physics, 2016, 55, 031302.	1.5	3
126	Impact of silicon quantum dot super lattice and quantum well structure as intermediate layer on pâ€iâ€n silicon solar cells. Progress in Photovoltaics: Research and Applications, 2016, 24, 774-780.	8.1	20

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127	Effects of deposition rate on the structure and electron density of evaporated BaSi2 films. Journal of Applied Physics, 2016, 120, 045103.	2.5	28
128	Novel light trapping structure by alkaline etching using a Ge dot mask for crystalline Si solar cells. , 2016, , .		3
129	Application of new doping techniques to solar cells for low temperature fabrication. , 2016, , .		1
130	p-BaSi2/n-Si heterojunction solar cells with conversion efficiency reaching 9.0%. Applied Physics Letters, 2016, 108, .	3.3	69
131	Control of the electrical properties of BaSi<inf>2</inf> evaporated films for solar cell applications. , 2016, , .		0
132	Improved multicrystalline silicon ingot quality using single layer silicon beads coated with silicon nitride as seed layer. Journal of Crystal Growth, 2016, 441, 124-130.	1.5	13
133	Effect of passivation layer grown by atomic layer deposition and sputtering processes on Si quantum dot superlattice to generate high photocurrent for high-efficiency solar cells. Japanese Journal of Applied Physics, 2016, 55, 032303.	1.5	9
134	Modulated surface nanostructures for enhanced light trapping and reduced surface reflection of crystalline silicon solar cells. Japanese Journal of Applied Physics, 2016, 55, 052302.	1.5	4
135	Effects of the Si/Al layer thickness on the continuity, crystalline orientation and the growth kinetics of the poly-Si thin films formed by aluminum-induced crystallization. Thin Solid Films, 2016, 616, 213-219.	1.8	19
136	Light-induced Recovery of Effective Carrier Lifetime in Boron-doped Czochralski Silicon at Room Temperature. Energy Procedia, 2016, 92, 801-807.	1.8	1
137	Evidence for efficient passivation of vertical silicon nanowires by anodic aluminum oxide. Solar Energy Materials and Solar Cells, 2016, 157, 393-398.	6.2	5
138	Effect of grain boundary character of multicrystalline Si on external and internal (phosphorus) gettering of impurities. Progress in Photovoltaics: Research and Applications, 2016, 24, 1615-1625.	8.1	6
139	Photoresponse properties of BaSi₂film grown on Si (100) by vacuum evaporation. Materials Research Express, 2016, 3, 076204.	1.6	21
140	Growth direction control of dendrite crystals in parallel direction to realize high-quality multicrystalline silicon ingot. Japanese Journal of Applied Physics, 2016, 55, 091302.	1.5	2
141	Control of electrical properties of BaSi2 thin films by alkali-metal doping using alkali-metal fluorides. Thin Solid Films, 2016, 603, 218-223.	1.8	6
142	Simple Vacuum Evaporation Route to BaSi2 Thin Films for Solar Cell Applications. Procedia Engineering, 2016, 141, 27-31.	1.2	20
143	On the Mechanism of BaSi2 Thin Film Formation on Si Substrate by Vacuum Evaporation. Procedia Engineering, 2016, 141, 23-26.	1.2	21
144	Influence of surface roughness of ZnO layer on the growth of polycrystalline Si layer via aluminum-induced layer exchange process. Journal of Advanced Marine Engineering and Technology, 2016, 40, 692-697.	0.4	0

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145	Cross-sectional electric field distributions in BaSi2 homo and BaSi2/Si hetero pn junctions. , 2015, , .		1
146	Application of heterojunction to Si-based solar cells using photonic nanostructures coupled with vertically aligned Ge quantum dots. Japanese Journal of Applied Physics, 2015, 54, 08KA06.	1.5	1
147	Control of surface dip diameter in Si-based photonic nanostructures by changing growth temperature of Ge quantum dot multilayer structures and its impact on their optical properties. Japanese Journal of Applied Physics, 2015, 54, 08KA01.	1.5	5
148	Seed manipulation for artificially controlled defect technique in new growth method for quasi-monocrystalline Si ingot based on casting. Applied Physics Express, 2015, 8, 105501.	2.4	38
149	Comparison of phosphorus gettering effect in faceted dendrite and small grain of multicrystalline silicon wafers grown by floating cast method. Japanese Journal of Applied Physics, 2015, 54, 08KD11.	1.5	1
150	Influence of Substrate on Crystal Orientation of Large-Grained Si Thin Films Formed by Metal-Induced Crystallization. International Journal of Photoenergy, 2015, 2015, 1-7.	2.5	10
151	Relationship between dislocation density and contact angle of dendrite crystals in practical size silicon ingot. Journal of Applied Physics, 2015, 117, .	2.5	12
152	Structural control of dendrite crystals in practical size silicon ingots grown by floating cast method. , 2015, , .		0
153	Realization of single-phase BaSi₂films by vacuum evaporation with suitable optical properties and carrier lifetime for solar cell applications. Japanese Journal of Applied Physics, 2015, 54, 07JE02.	1.5	41
154	Fabrication of single-phase polycrystalline BaSi₂thin films on silicon substrates by vacuum evaporation for solar cell applications. Japanese Journal of Applied Physics, 2015, 54, 08KC03.	1.5	31
155	Fabrication and characterization of BaSi2 films on Ge(111) substrates by molecular beam epitaxy. , 2015, , .		1
156	Cross-sectional potential profile across a BaSi2pn junction by Kelvin probe force microscopy. Japanese Journal of Applied Physics, 2015, 54, 030306.	1.5	5
157	Suppression of metastable-phase inclusion in N-polar (0001Â¯) InGaN/GaN multiple quantum wells grown by metalorganic vapor phase epitaxy. Applied Physics Letters, 2015, 106, .	3.3	6
158	Effects of anodization process of aluminum oxide template fabrication on selective growth of Si nanowire arrays. Japanese Journal of Applied Physics, 2015, 54, 08KA02.	1.5	2
159	Formation of BaSi2 heterojunction solar cells using transparent MoOx hole transport layers. Applied Physics Letters, 2015, 106, .	3.3	19
160	Selective growth of vertical silicon nanowire array guided by anodic aluminum oxide template. Japanese Journal of Applied Physics, 2015, 54, 095003.	1.5	3
161	Absorption enhancement in nanotextured solar cells with Ge/Si heterostructures. Japanese Journal of Applied Physics, 2015, 54, 04DR03.	1.5	3
162	Structural and electrical characterizations of crack-free BaSi2 thin films fabricated by thermal evaporation. Thin Solid Films, 2015, 595, 68-72.	1.8	31

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163	Grazing-incidence small-angle X-ray scattering from Ge nanodots self-organized on Si(001) examinedÂwith soft X-rays. Journal of Synchrotron Radiation, 2014, 21, 161-164.	2.4	10
164	Fabrication and characterization of BaSi₂ epitaxial films over 1 Âµm in thickness on Si(111). Japanese Journal of Applied Physics, 2014, 53, 04ER04.	1.5	31
165	Electrical and optical characterizations of an n-BaSi<inf>2</inf>/p-Si hetero-junction for solar cell applications. , 2014, , .		0
166	Simulation study of Ge/Si heterostructure solar cells yielding improved open-circuit voltage and quantum efficiency. Japanese Journal of Applied Physics, 2014, 53, 110312.	1.5	0
167	Grain boundaries characterization of semiconducting BaSi<inf>2</inf> thin films on a polycrystalline Si substrate. , 2014, , .		0
168	Potential variation around grain boundaries in BaSi2 films grown on multicrystalline silicon evaluated using Kelvin probe force microscopy. Journal of Applied Physics, 2014, 116, .	2.5	8
169	Light trapping by direction-dependent light transmission in front-surface photonic nanostructures. Applied Physics Express, 2014, 7, 122301.	2.4	6
170	Optical Properties of Quantum-Dot-Based Surface Photonic Nanostructures in Ge/Si Quantum Dot Solar Cells. , 2014, , .		0
171	Low-temperature (180â€‰Â°C) formation of large-grained Ge (111) thin film on insulator using accelerated metal-induced crystallization. Applied Physics Letters, 2014, 104, .	3.3	96
172	Engineering of p-n junction for high efficiency semiconducting BaSi2 based thin film solar cells. , 2014, , .		0
173	Selective formation of large-grained, (100)- or (111)-oriented Si on glass by Al-induced layer exchange. Journal of Applied Physics, 2014, 115, .	2.5	40
174	Investigation of the cause of reduced open circuit voltage in Ge/Si quantum dot solar cells. , 2014, , .		0
175	Improvement of annealing procedure to suppress defect generation during impurity gettering in multicrystalline silicon for solar cells. , 2014, , .		0
176	Light trapping in large-scale photonic nanostructures fabricated from vertically aligned Ge quantum dots on crystalline silicon. , 2014, , .		0
177	Al-induced crystallization of amorphous Ge thin films on conducting layer coated glass substrates. Japanese Journal of Applied Physics, 2014, 53, 04EH01.	1.5	7
178	Structural characterization of polycrystalline Ge thin films on insulators formed by diffusion-enhanced Al-induced layer exchange. Japanese Journal of Applied Physics, 2014, 53, 04EH03.	1.5	7
179	Enhanced photocarrier generation in large-scale photonic nanostructures fabricated from vertically aligned quantum dots. Optics Express, 2014, 22, A225.	3.4	9
180	Effect of miniband formation in a quantum dot super lattice fabricated by combination of bio-template and neutral beam etching for high efficiency quantum dot solar cells. , 2014, , .		0

#	Article	IF	Citations
181	Potential variations around grain boundaries in impurity-doped BaSi2 epitaxial films evaluated by Kelvin probe force microscopy. Journal of Applied Physics, 2014, 116, .	2.5	23
182	Influence of grain size and surface condition on minority-carrier lifetime in undoped n-BaSi2 on Si(111). Journal of Applied Physics, 2014, 115, .	2.5	80
183	N-type doping of BaSi2 epitaxial films by arsenic ion implantation through a dose-dependent carrier generation mechanism. Thin Solid Films, 2014, 567, 105-108.	1.8	22
184	Si-based new material for high-efficiency thin film solar cells. , 2014, , .		0
185	Enhanced Phosphorus Gettering of Impurities in Multicrystalline Silicon at Low Temperature. Energy Procedia, 2014, 55, 203-210.	1.8	8
186	Mono-Like Silicon Growth Using Functional Grain Boundaries to Limit Area of Multicrystalline Grains. IEEE Journal of Photovoltaics, 2014, 4, 84-87.	2.5	48
187	Orientation control of Ge thin films by underlayer-selected Al-induced crystallization. CrystEngComm, 2014, 16, 2578.	2.6	17
188	Precipitation control and activation enhancement in boron-doped p+-BaSi2 films grown by molecular beam epitaxy. Applied Physics Letters, 2014, 104, .	3.3	32
189	Analysis of the electrical properties of Cr/n-BaSi2 Schottky junction and n-BaSi2/p-Si heterojunction diodes for solar cell applications. Journal of Applied Physics, 2014, 115, .	2.5	49
190	Evaluation of minority carrier diffusion length of undoped n-BaSi₂epitaxial thin films on Si(001) substrates by electron-beam-induced-current technique. Japanese Journal of Applied Physics, 2014, 53, 078004.	1.5	20
191	Growth promotion of Al-induced crystallized Ge films on insulators by insertion of a Ge membrane below the Al layer. Thin Solid Films, 2014, 557, 143-146.	1.8	16
192	Large-grained (111)-oriented Si/Al/SiO2 structures formed by diffusion-controlled Al-induced layer exchange. Thin Solid Films, 2014, 557, 147-150.	1.8	7
193	N-type doping of BaSi2 epitaxial films by phosphorus ion implantation and thermal annealing. Thin Solid Films, 2014, 557, 90-93.	1.8	26
194	Simple approach for improving gold deposition inside nanoporous alumina template on Si substrate. Applied Surface Science, 2014, 305, 9-15.	6.1	4
195	Control of geometry in Si-based photonic nanostructures formed by maskless wet etching process and its impact on optical properties. Thin Solid Films, 2014, 557, 338-341.	1.8	9
196	Formation process of Si3N4 particles on surface of Si ingots grown using silica crucibles with Si3N4 coating by noncontact crucible method. Journal of Crystal Growth, 2014, 389, 112-119.	1.5	20
197	Towards implementation of floating cast method for growing large-scale high-quality multicrystalline silicon ingot using designed double crucibles. Progress in Photovoltaics: Research and Applications, 2014, 22, 726-732.	8.1	12
198	Carrier extraction dynamics from Ge/Si quantum wells in Si solar cells. Thin Solid Films, 2014, 557, 368-371.	1.8	10

#	Article	IF	Citations
199	Geometry Control of Si-based Photonic Nanostructures Coupled with Quantum Dot Multilayers and Integration to Crystalline Si Solar Cells. , 2014, , .		0
200	Enhanced photocarrier generation in large-scale photonic nanostructures fabricated from vertically aligned quantum dots. Optics Express, 2014, 22, A225-32.	3.4	1
201	Temperature dependent Al-induced crystallization of amorphous Ge thin films on SiO2 substrates. Journal of Crystal Growth, 2013, 372, 189-192.	1.5	16
202	Orientation Control of Large-Grained Si Films on Insulators by Thickness-Modulated Al-Induced Crystallization. Crystal Growth and Design, 2013, 13, 1767-1770.	3.0	44
203	Lattice and grain-boundary diffusions of boron atoms in BaSi2 epitaxial films on Si(111). Journal of Applied Physics, 2013, 113, .	2.5	21
204	In-situ heavily p-type doping of over 1020â€‰cmâ^'3 in semiconducting BaSi2 thin films for solar cells applications. Applied Physics Letters, 2013, 102, .	3.3	72
205	Generation of high photocurrent in three-dimensional silicon quantum dot superlattice fabricated by combining bio-template and neutral beam etching for quantum dot solar cells. Nanoscale Research Letters, 2013, 8, 228.	5.7	7
206	High photo-current generation in a three-dimensional silicon quantum dot superlattice fabricated by combination of bio-template and neutral beam etching for quantum dot solar cell. , 2013, , .		2
207	Investigation of the open-circuit voltage in solar cells doped with quantum dots. Scientific Reports, 2013, 3, 2703.	3.3	65
208	Theory of open-circuit voltage and the driving force of charge separation in pn-junction solar cells. Journal of Applied Physics, 2013, 114, .	2.5	19
209	Effect of Ge/Si heterostructures on carrier extraction in Si solar cells with Ge quantum dots. , 2013, , .		0
210	Characterization of grain boundary properties in BaSi2 epitaxial films on Si(111) and Si(001) by Kelvin probe force microscopy. , 2013, , .		0
211	Type-II Ge/Si quantum dot superlattice for intermediate-band solar cell applications. , 2013, , .		1
212	Improvement of excess-carrier lifetime in BaSi<inf>2</inf> epitaxial films by post-growth annealing. , 2013, , .		0
213	Enhancement of light emission from Ge quantum dots by photonic crystal nanocavities at room-temperature. Journal of Crystal Growth, 2013, 378, 636-639.	1.5	21
214	Molecular beam epitaxy of boron doped p-type BaSi2 epitaxial films on Si(111) substrates for thin-film solar cells. Journal of Crystal Growth, 2013, 378, 201-204.	1.5	18
215	Structural study on phosphorus doping of BaSi2 epitaxial films by ion implantation. Thin Solid Films, 2013, 534, 470-473.	1.8	15
216	Formation of large-grain-sized BaSi2 epitaxial layers grown on Si(111) by molecular beam epitaxy. Journal of Crystal Growth, 2013, 378, 193-197.	1.5	5

#	Article	IF	Citations
217	On the origin of the uniaxial strain induced in Si/Ge heterostructures with selective ion implantation technique. Journal of Crystal Growth, 2013, 378, 251-253.	1.5	4
218	Gas-source MBE growth of strain-relaxed Si1â^'xCx on Si(100) substrates. Journal of Crystal Growth, 2013, 378, 212-217.	1.5	2
219	Large photoresponsivity in semiconducting BaSi2 epitaxial films grown on Si(001) substrates by molecular beam epitaxy. Journal of Crystal Growth, 2013, 378, 198-200.	1.5	4
220	Effects of formation of mini-bands in two-dimensional array of silicon nanodisks with SiC interlayer for quantum dot solar cells. Nanotechnology, 2013, 24, 015301.	2.6	20
221	Reflectance anisotropies of compressively strained Si grown on vicinal Si1â^'xCx(001). Applied Physics Letters, 2013, 102, 011902.	3.3	1
222	Effects of crystal defects and their interactions with impurities on electrical properties of multicrystalline Si. Journal of Applied Physics, 2013, 113, 133503.	2.5	21
223	Formation of compressively strained Si/Si1â^'xCx/Si(100) heterostructures using gas-source molecular beam epitaxy. Journal of Crystal Growth, 2013, 362, 276-281.	1.5	9
224	On the growth mechanism of polycrystalline silicon thin film by Al-induced layer exchange process. Journal of Crystal Growth, 2013, 362, 16-19.	1.5	9
225	Effect of Ga content and growth temperature on Cu(In,Ga)Se₂ thin film deposited on heatâ€resistant glass substrates. Physica Status Solidi C: Current Topics in Solid State Physics, 2013, 10, 1035-1037.	0.8	7
226	Double-Layered Ge Thin Films on Insulators Formed by an Al-Induced Layer-Exchange Process. Crystal Growth and Design, 2013, 13, 3908-3912.	3.0	17
227	Large-Grained Polycrystalline (111) Ge Films on Insulators by Thickness-Controlled Al-Induced Crystallization. ECS Journal of Solid State Science and Technology, 2013, 2, Q195-Q199.	1.8	17
228	Formation of Uniaxially Strained Si/Ge Channels on SiGe Buffers Strain-Controlled with Selective Ion Implantation. ECS Transactions, 2013, 50, 815-820.	0.5	0
229	TEM Analysis of the Nanostructure of Pb(Mg_{1/3}Nb_{2/3})O₃ Thin Films by MOD Method. Key Engineering Materials, 2013, 582, 19-22.	0.4	2
230	Control of Dip Shape in Photonic Nanostructures by Maskless Wet-Etching Process and Its Impact on Optical Properties. Japanese Journal of Applied Physics, 2013, 52, 080202.	1.5	7
231	Nano-Structure around 90Â° Domain Wall and Elastic Interaction with Misfit Dislocation in PbTiO₃ Thin Film. Key Engineering Materials, 2013, 566, 167-170.	0.4	1
232	Control of Grain Boundary Propagation in Mono-Like Si: Utilization of Functional Grain Boundaries. Applied Physics Express, 2013, 6, 025505.	2.4	50
233	Enhanced p-type conductivity and band gap narrowing in heavily B-doped p-BaSi<inf>2</inf> films grown by molecular beam epitaxy. , 2013, , .		0
234	Evaluation of potential variations around grain boundaries in BaSi2 epitaxial films by Kelvin probe force microscopy. Applied Physics Letters, 2013, 103, .	3.3	29

#	Article	IF	Citations
235	Growth of vertical silicon nanowires array using electrochemical alternative. , 2013, , .		2
236	Mechanism of strain relaxation in BaSi₂ epitaxial films on Si(111) substrates during postâ€growth annealing and application for film exfoliation. Physica Status Solidi C: Current Topics in Solid State Physics, 2013, 10, 1677-1680.	0.8	16
237	Determination of Bulk Minority-Carrier Lifetime in BaSi₂Earth-Abundant Absorber Films by Utilizing a Drastic Enhancement of Carrier Lifetime by Post-Growth Annealing. Applied Physics Express, 2013, 6, 112302.	2.4	75
238	Nanostructure and Strain Field in Vertically Aligned Nano-Islands for Si/Ge 2D Photonic Nanocrystals.. Materials Research Society Symposia Proceedings, 2013, 1510, 1.	0.1	2
239	Fabrication and characterizations of phosphorusâ€doped nâ€type BaSi₂ epitaxial films grown by molecular beam epitaxy. Physica Status Solidi C: Current Topics in Solid State Physics, 2013, 10, 1753-1755.	0.8	15
240	Investigation of the tunneling properties and surface morphologies of BaSi2 /Si tunnel junctions for BaSi2 solar cell applications. Physica Status Solidi C: Current Topics in Solid State Physics, 2013, 10, 1765-1768.	0.8	1
241	Effect of Ge/Al thickness on Al-induced crystallization of amorphous Ge layers on glass substrates. Physica Status Solidi C: Current Topics in Solid State Physics, 2013, 10, 1781-1784.	0.8	0
242	Fabrication of BaSi2 films on (111)-oriented Si layers formed by inverted Al-induced crystallization method on glass structure. Physica Status Solidi C: Current Topics in Solid State Physics, 2013, 10, 1769-1772.	0.8	1
243	Epitaxial growth of BaSi2films with large grains using vicinal Si(111) substrates. Physica Status Solidi C: Current Topics in Solid State Physics, 2013, 10, 1756-1758.	0.8	1
244	Silicon-based current-injected light emitting diodes with Ge self-assembled quantum dots embedded in photonic crystal nanocavities. Optics Express, 2012, 20, 14714.	3.4	21
245	Influence of Thermal Annealing on the Carrier Extraction in Ge/Si Quantum Dot Solar Cells. Japanese Journal of Applied Physics, 2012, 51, 10NE24.	1.5	6
246	Quantum dot solar cells using 2-dimensional array of 6.4-nm-diameter silicon nanodisks fabricated using bio-templates and neutral beam etching. Applied Physics Letters, 2012, 101, 063121.	3.3	15
247	Growth of multicrystalline silicon ingot from the top of the melt: Control of microstructures and reduction of stress. , 2012, , .		1
248	Upper limit of two-dimensional hole gas mobility in strained Ge/SiGe heterostructures. Applied Physics Letters, 2012, 100, .	3.3	23
249	Realization of Large-Domain Barium Disilicide Epitaxial Thin Film by Introduction of Miscut to Si(111) Substrate. Japanese Journal of Applied Physics, 2012, 51, 10NB06.	1.5	2
250	Effect of Phase Purity on Dislocation Density of Pressurized-Reactor Metalorganic Vapor Phase Epitaxy Grown InN. Japanese Journal of Applied Physics, 2012, 51, 04DH02.	1.5	5
251	Effect of Solid-Phase-Epitaxy Si Layers on Suppression of Sb Diffusion from Sb-Doped n⁺-BaSi₂/p⁺-Si Tunnel Junction to Undoped BaSi₂ Overlayers. Japanese Journal of Applied Physics, 2012, 51, 04DP01.	1.5	1
252	Epitaxy of Orthorhombic BaSi$_{2}$ with Preferential In-Plane Crystal Orientation on Si(001): Effects of Vicinal Substrate and Annealing Temperature. Japanese Journal of Applied Physics, 2012, 51, 095501.	1.5	15

#	Article	IF	Citations
253	Molecular Beam Epitaxy of BaSi$_{2}$ Films with Grain Size over 4 mum on Si(111). Japanese Journal of Applied Physics, 2012, 51, 098003.	1.5	18
254	High efficiency quantum dot solar cells using 2-dimensional 6.4-nm-diameter Si nanodisk with SiC interlayer. , 2012, , .		0
255	Growth of multicrystalline Si ingots for solar cells using noncontact crucible method without touching the crucible wall. , 2012, , .		1
256	Room-Temperature Electroluminescence from Ge Quantum Dots Embedded in Photonic Crystal Microcavities. Applied Physics Express, 2012, 5, 052101.	2.4	10
257	Highly (111)-oriented Ge thin films on insulators formed by Al-induced crystallization. Applied Physics Letters, 2012, 101, 072106.	3.3	88
258	Formation of polycrystalline silicon films with μm-order-long grains through liquid-phase explosive crystallization by flash lamp annealing. , 2012, , .		0
259	Improved internal quantum efficiency in high-quality BaSi<inf>2</inf> films grown by molecular beam epitaxy. , 2012, , .		0
260	Investigation of the carrier recombination process in undoped barium disilicide epitaxial films. , 2012, , .		0
261	Large-Grain Polycrystalline Silicon Films Formed through Flash-Lamp-Induced Explosive Crystallization. Japanese Journal of Applied Physics, 2012, 51, 10NB15.	1.5	8
262	Lateral PIN current-injected photonic crystal nanocavity light emitting diodes based on Ge quantum dots. , 2012, , .		1
263	Enhanced carrier extraction under strong light irradiation in Ge/Si type-II quantum dot solar cells. , 2012, , .		0
264	Enhanced carrier extraction from Ge quantum dots in Si solar cells under strong photoexcitation. Applied Physics Letters, 2012, 101, .	3.3	43
265	Molecular beam epitaxy of BaSi2 thin films on Si(001) substrates. Journal of Crystal Growth, 2012, 345, 16-21.	1.5	61
266	Growth of multicrystalline Si ingots using noncontact crucible method for reduction of stress. Journal of Crystal Growth, 2012, 344, 6-11.	1.5	42
267	Investigation of grain boundaries in BaSi2 epitaxial films on Si(1 1 1) substrates using transmission electron microscopy and electron-beam-induced current technique. Journal of Crystal Growth, 2012, 348, 75-79.	1.5	133
268	Growth velocity and grain size of multicrystalline solar cell silicon. Journal of Crystal Growth, 2012, 356, 17-21.	1.5	10
269	Dependence of crystal orientation in Al-induced crystallized poly-Si layers on SiO2 insertion layer thickness. Journal of Crystal Growth, 2012, 356, 65-69.	1.5	21
270	Silicon-Based Light-Emitting Devices Based on Ge Self-Assembled Quantum Dots Embedded in Optical Cavities. IEEE Journal of Selected Topics in Quantum Electronics, 2012, 18, 1830-1838.	2.9	28

#	Article	IF	Citations
271	Improved photoresponsivity of semiconducting BaSi₂ epitaxial films grown on a tunnel junction for thin-film solar cells. Applied Physics Letters, 2012, 100, 152114.	3.3	50
272	Investigation of the recombination mechanism of excess carriers in undoped BaSi2 films on silicon. Journal of Applied Physics, 2012, 112, .	2.5	84
273	Simultaneous enhanced photon capture and carrier generation in Si solar cells using Ge quantum dot photonic nanocrystals. Nanotechnology, 2012, 23, 185401.	2.6	36
274	Effect of Phase Purity on Dislocation Density of Pressurized-Reactor Metalorganic Vapor Phase Epitaxy Grown InN. Japanese Journal of Applied Physics, 2012, 51, 04DH02.	1.5	9
275	Effect of Solid-Phase-Epitaxy Si Layers on Suppression of Sb Diffusion from Sb-Doped n⁺-BaSi₂/p⁺-Si Tunnel Junction to Undoped BaSi₂Overlayers. Japanese Journal of Applied Physics, 2012, 51, 04DP01.	1.5	1
276	Epitaxy of Orthorhombic BaSi2with Preferential In-Plane Crystal Orientation on Si(001): Effects of Vicinal Substrate and Annealing Temperature. Japanese Journal of Applied Physics, 2012, 51, 095501.	1.5	2
277	Realization of Large-Domain Barium Disilicide Epitaxial Thin Film by Introduction of Miscut to Si(111) Substrate. Japanese Journal of Applied Physics, 2012, 51, 10NB06.	1.5	1
278	Large-Grain Polycrystalline Silicon Films Formed through Flash-Lamp-Induced Explosive Crystallization. Japanese Journal of Applied Physics, 2012, 51, 10NB15.	1.5	4
279	Influence of Thermal Annealing on the Carrier Extraction in Ge/Si Quantum Dot Solar Cells. Japanese Journal of Applied Physics, 2012, 51, 10NE24.	1.5	2
280	Molecular Beam Epitaxy of BaSi2Films with Grain Size over 4 Âµm on Si(111). Japanese Journal of Applied Physics, 2012, 51, 098003.	1.5	2
281	Generation mechanism of dislocations and their clusters in multicrystalline silicon during two-dimensional growth. Journal of Applied Physics, 2011, 110, 083530.	2.5	23
282	Line Width Dependence of Anisotropic Strain State in SiGe Films Induced by Selective Ion Implantation. Applied Physics Express, 2011, 4, 095701.	2.4	9
283	Formation mechanism of twin boundaries during crystal growth of silicon. Scripta Materialia, 2011, 65, 556-559.	5.2	27
284	Formation of poly-Si layers on AZO/<mml:math altimg="si1.gif" display="inline" overflow="scroll" xmlns:xocs="http://www.elsevier.com/xml/xocs/dtd" xmlns:xs="http://www.w3.org/2001/XMLSchema" xmlns:xsi="http://www.w3.org/2001/XMLSchema-instance" xmlns="http://www.elsevier.com/xml/ja/dtd" xmlns:ja="http://www.elsevier.com/xml/ja/dtd" xmlns:mml="http://www.w3.org/1998/Math/MathML" xmlns:tb="http://www.elsevier.com/xml/common/table/dtd" xmlns:sb="http://www.elsevier.com/xml/common/struct-bib/dtd" xmlns:ce="http. Physics Procedia, 2011	1.2	3
285	Fabrication of BaSi2 films on transparent CaF2 (111) substrates by molecular beam epitaxy for optical characterization. Physics Procedia, 2011, 11, 189-192.	1.2	2
286	Effects of increased compressive strain on hole effective mass and scattering mechanisms in strained Ge channels. Microelectronic Engineering, 2011, 88, 465-468.	2.4	6
287	In situObservation of Polycrystalline Silicon Thin Films Grown Using Aluminum-Doped Zinc Oxide on Glass Substrate by the Aluminum-Induced Crystallization. Japanese Journal of Applied Physics, 2011, 50, 04DP02.	1.5	1
288	Drastic reduction of crystallization time during Al-induced crystallizaion of amorphous Si by Ge adlayer. , 2011, , .		0

#	Article	IF	Citations
289	Implementation of faceted dendrite growth on floating cast method to realize high-quality multicrsytalline Si ingot for solar cells. Journal of Applied Physics, 2011, 109, .	2.5	20
290	Impact of type of crystal defects in multicrystalline Si on electrical properties and interaction with impurities. Journal of Applied Physics, 2011, 109, .	2.5	22
291	Types of siliconâ€“germanium (SiGe) bulk crystal growth methods and their applications. , 2011, , 72-82.		3
292	Configuration and local elastic interaction of ferroelectric domains and misfit dislocation in PbTiO₃/SrTiO₃epitaxial thin films. Science and Technology of Advanced Materials, 2011, 12, 034413.	6.1	41
293	Structural Study of BF₂ Ion Implantation and Post Annealing of BaSi₂ Epitaxial Films. Japanese Journal of Applied Physics, 2011, 50, 121202.	1.5	11
294	Siliconâ€“germanium (SiGe) nanostructures. , 2011, , .		28
295	In situObservation of Polycrystalline Silicon Thin Films Grown Using Aluminum-Doped Zinc Oxide on Glass Substrate by the Aluminum-Induced Crystallization. Japanese Journal of Applied Physics, 2011, 50, 04DP02.	1.5	5
296	Structural Study of BF2Ion Implantation and Post Annealing of BaSi2Epitaxial Films. Japanese Journal of Applied Physics, 2011, 50, 121202.	1.5	2
297	Generation mechanism of dislocations during directional solidification of multicrystalline silicon using artificially designed seed. Journal of Crystal Growth, 2010, 312, 897-901.	1.5	96
298	Impact of amorphous Ge thin layer at the amorphous Si/Al interface on Al-induced crystallization. Journal of Crystal Growth, 2010, 312, 3257-3260.	1.5	7
299	Pattern formation mechanism of a periodically faceted interface during crystallization ofSi. Journal of Crystal Growth, 2010, 312, 3670-3674.	1.5	13
300	Formation of uniaxially strained SiGe by selective ion implantation technique. Thin Solid Films, 2010, 518, 2454-2457.	1.8	2
301	Ion energy and dose dependence of strain relaxation for thin SiGe buffer layers using Si+ implantation. Thin Solid Films, 2010, 518, S162-S164.	1.8	3
302	Evaluation of minority carrier lifetime in BaSi<inf>2</inf> as a novel material for earth-abundant high efficiency thin film solar cells. , 2010, , .		1
303	Photoresponse properties of BaSi<inf>2</inf> films on N⁺-BaSi<inf>2</inf>/P⁺-Si tunnel junction for high efficiency thin film solar cells. , 2010, , .		0
304	Direct bandgap measurements in a three-dimensionally macroporous silicon 9R polytype using monochromated transmission electron microscope. Applied Physics Letters, 2010, 97, .	3.3	11
305	Ion dose, energy, and species dependencies of strain relaxation of SiGe buffer layers fabricated by ion implantation technique. Journal of Applied Physics, 2010, 107, 103509.	2.5	11
306	Optical anisotropies of Si grown on step-graded SiGe(110) layers. Applied Physics Letters, 2010, 96, 091904.	3.3	4

#	Article	IF	Citations
307	Growth mechanism of the SiâŸ¨110âŸ©faceted dendrite. Physical Review B, 2010, 81, .	3.2	26
308	High efficiency solar cells obtained from small size ingots with 30 cmΦ by controlling the distribution and orientation of dendrite crystals grown along the bottom of the ingots. , 2010, , .		5
309	Lattice-Latching Effect in Metalorganic Vapor Phase Epitaxy Growth of InGaAsN Film Lattice-Matched to Bulk InGaAs Substrate. Japanese Journal of Applied Physics, 2010, 49, 040202.	1.5	2
310	On the Controlling Mechanism of Preferential Orientation of Polycrystalline-Silicon Thin Films Grown by Aluminum-Induced Crystallization. Applied Physics Express, 2010, 3, 095803.	2.4	30
311	Epitaxial Growth and Photoresponse Properties of BaSi2Layers toward Si-Based High-Efficiency Solar Cells. Japanese Journal of Applied Physics, 2010, 49, 04DP05.	1.5	8
312	A grazing incidence small-angle x-ray scattering analysis on capped Ge nanodots in layer structures. Journal of Physics Condensed Matter, 2010, 22, 474003.	1.8	7
313	Computational Investigation of Relationship between Shear Stress and Multicrystalline Structure in Silicon. Japanese Journal of Applied Physics, 2010, 49, 04DP01.	1.5	16
314	Relationship between grain boundary structures in Si multicrystals and generation of dislocations during crystal growth. Journal of Applied Physics, 2010, 107, .	2.5	46
315	Room-temperature electroluminescence from Si microdisks with Ge quantum dots. Optics Express, 2010, 18, 13945.	3.4	54
316	Formation mechanism of twin boundaries in silicon multicrystals during crystal growth. , 2010, , .		0
317	Fabrication of n⁺-BaSi₂/p⁺-Si Tunnel Junction on Si(111) Surface by Molecular Beam Epitaxy for Photovoltaic Applications. Applied Physics Express, 2010, 3, 021301.	2.4	33
318	Formation mechanism of a faceted interface:In situobservation of the Si(100) crystal-melt interface during crystal growth. Physical Review B, 2009, 80, .	3.2	52
319	Current-injected light emitting device based on Si microdisk with Ge dots. , 2009, , .		0
320	Growth of Compositionally Graded SiGe Bulk Crystal and Its Application As Substrate with Lateral Variation in Ge Content. Japanese Journal of Applied Physics, 2009, 48, 115507.	1.5	2
321	Quantitative analysis of subgrain boundaries in Si multicrystals and their impact on electrical properties and solar cell performance. Journal of Applied Physics, 2009, 105, 044909.	2.5	27
322	Strain relaxation mechanisms in compositionally uniform and step-graded SiGe films grown on Si(1 1) Tj ETQq0 0 0 rgBT /Overlock 10 Tf	1.4	10
323	Crystalline morphologies of step-graded SiGe layers grown on exact and vicinal (110) Si substrates. Journal of Crystal Growth, 2009, 311, 809-813.	1.5	16
324	Structural and transport properties of strained SiGe grown on V-groove patterned Si(110) substrates. Journal of Crystal Growth, 2009, 311, 814-818.	1.5	4

#	Article	IF	Citations
325	Strain relaxation mechanisms in step-graded SiGe/Si(110) heterostructures grown by gas-source MBE at high temperatures. Journal of Crystal Growth, 2009, 311, 819-824.	1.5	14
326	Local control of strain in SiGe by ion-implantation technique. Journal of Crystal Growth, 2009, 311, 806-808.	1.5	3
327	Fabrication of thin strain-relaxed SiGe buffer layers with high Ge composition by ion implantation method. Journal of Crystal Growth, 2009, 311, 825-828.	1.5	9
328	Resonant photoluminescence from Ge self-assembled dots in optical microcavities. Journal of Crystal Growth, 2009, 311, 883-887.	1.5	7
329	Floating cast method to realize high-quality Si bulk multicrystals for solar cells. Journal of Crystal Growth, 2009, 311, 228-231.	1.5	35
330	Fabrication of (111)-oriented Si layers on SiO2 substrates by an aluminum-induced crystallization method and subsequent growth of semiconducting BaSi2 layers for photovoltaic application. Journal of Crystal Growth, 2009, 311, 3581-3586.	1.5	29
331	Growth behavior of faceted Si crystals at grain boundary formation. Journal of Crystal Growth, 2009, 312, 19-23.	1.5	8
332	Microstructures of Si multicrystals and their impact on minority carrier diffusion length. Acta Materialia, 2009, 57, 3268-3276.	7.9	39
333	Strain dependence of hole effective mass and scattering mechanism in strained Ge channel structures. Applied Physics Letters, 2009, 95, .	3.3	22
334	Generation and Wavelength Control of Resonant Luminescence from Silicon Photonic Crystal Microcavities with Ge Dots. Japanese Journal of Applied Physics, 2009, 48, 022102.	1.5	13
335	Effect of reflected waves on the GISAXS analysis of as-grown capped Ge nanodots. Journal of Physics: Conference Series, 2009, 184, 012005.	0.4	0
336	Fundamental Understanding of Subgrain Boundaries. Advances in Materials Research, 2009, , 83-95.	0.2	2
337	Room-temperature light-emission from Ge quantum dots in photonic crystals. Thin Solid Films, 2008, 517, 125-127.	1.8	4
338	Growth temperature dependence of the crystalline morphology of SiGe films grown on Si(110) substrates with compositionally step-graded buffer. Thin Solid Films, 2008, 517, 235-238.	1.8	10
339	Influence of growth temperature and cooling rate on the growth of Si epitaxial layer by dropping-type liquid phase epitaxy from the pure Si melt. Journal of Crystal Growth, 2008, 310, 5248-5251.	1.5	3
340	Hole density and strain dependencies of hole effective mass in compressively strained Ge channel structures. Physica E: Low-Dimensional Systems and Nanostructures, 2008, 40, 2122-2124.	2.7	0
341	In situ observation of Si faceted dendrite growth from low-degree-of-undercooling melts. Acta Materialia, 2008, 56, 2663-2668.	7.9	82
342	Poly-Si films with long carrier lifetime prepared by rapid thermal annealing of Cat-CVD amorphous silicon thin films. Thin Solid Films, 2008, 516, 600-603.	1.8	5

#	Article	IF	Citations
343	Characterizations of polycrystalline SiGe films on SiO2 grown by gas-source molecular beam deposition. Thin Solid Films, 2008, 517, 254-256.	1.8	0
344	Application of SiGe bulk crystal as a substrate for strain-controlled heterostructure materials. Thin Solid Films, 2008, 517, 14-16.	1.8	12
345	Floating Cast Method as a New Growth Method of Silicon Bulk Multicrystals for Solar Cells. Advances in Materials Research, 2008, , 149-156.	0.2	1
346	Vacancy formation during oxidation of silicon crystal surface. Applied Physics Letters, 2008, 93, 101904.	3.3	3
347	Functional Enhancement of Metalâ€“Semiconductorâ€“Metal Infrared Photodetectors on Heteroepitaxial SiGe-on-Si Using the Anodic Oxidation/Passivation Method. Japanese Journal of Applied Physics, 2008, 47, 2927-2931.	1.5	0
348	Acceptorlike Behavior of Defects in SiGe Alloys Grown by Molecular Beam Epitaxy. Japanese Journal of Applied Physics, 2008, 47, 4630.	1.5	20
349	Impact of Defect Density in Si Bulk Multicrystals on Gettering Effect of Impurities. Japanese Journal of Applied Physics, 2008, 47, 8790-8792.	1.5	11
350	Growth Mechanism of Si-Faceted Dendrites. Physical Review Letters, 2008, 101, 055503.	7.8	66
351	Structural Origin of a Cluster of Bright Spots in Reverse Bias Electroluminescence Image of Solar Cells Based on Si Multicrystals. Applied Physics Express, 2008, 1, 075001.	2.4	14
352	On Effects of Gate Bias on Hole Effective Mass and Mobility in Strained-Ge Channel Structures. Applied Physics Express, 2008, 1, 011401.	2.4	5
353	Ge dots in Optical Microcavities--A Possible Direction for Silicon-based Light Emitting Devices. ECS Transactions, 2008, 16, 857-864.	0.5	0
354	High-Quality Si Multicrystals with Same Grain Orientation and Large Grain Size by the Newly Developed Dendritic Casting Method for High-Efficiency Solar Cell Applications. Advances in Materials Research, 2008, , 123-140.	0.2	4
355	Growth of High-Quality Polycrystalline Si Ingot with Same Grain Orientation by Using Dendritic Casting Method. Advances in Materials Research, 2008, , 141-147.	0.2	2
356	High-Quality Polycrystalline Silicon Films with Minority Carrier Lifetimes over 5 Âµs Formed by Flash Lamp Annealing of Precursor Amorphous Silicon Films Prepared by Catalytic Chemical Vapor Deposition. Japanese Journal of Applied Physics, 2007, 46, 7198.	1.5	29
357	Improvement in the conversion efficiency of single-junction SiGe solar cells by intentional introduction of the compositional distribution. Journal of Applied Physics, 2007, 101, 054504.	2.5	7
358	Application of Czochralski-grown SiGe bulk crystal as a substrate for luminescent strained quantum wells. Applied Physics Letters, 2007, 90, 181914.	3.3	6
359	Control of strain status in SiGe thin film by epitaxial growth on Si with buried porous layer. Applied Physics Letters, 2007, 90, 031915.	3.3	3
360	Modification of local structures in multicrystals revealed by spatially resolved x-ray rocking curve analysis. Journal of Applied Physics, 2007, 102, 103504.	2.5	12

#	Article	IF	Citations
361	Silicon-based light emitters fabricated by embedding Ge self-assembled quantum dots in microdisks. Applied Physics Letters, 2007, 91, .	3.3	42
362	Modification of Local Structure and Its Influence on Electrical Activity of Near (310) Σ5 Grain Boundary in Bulk Silicon. Materials Transactions, 2007, 48, 143-147.	1.2	18
363	Enhanced Light Emission from Ge Quantum Dots in Microdisks. Conference Proceedings - Lasers and Electro-Optics Society Annual Meeting-LEOS, 2007, , .	0.0	0
364	Step-Induced Anisotropic Growth of Pentacene Thin Film Crystals on a Hydrogen-Terminated Si(111) Surface. Crystal Growth and Design, 2007, 7, 439-444.	3.0	13
365	SiGe double barrier resonant tunneling diodes on bulk SiGe substrates with high peak-to-valley current ratio. Applied Physics Letters, 2007, 91, .	3.3	8
366	Influence of structural imperfection of Î£5 grain boundaries in bulk multicrystalline Si on their electrical activities. Journal of Applied Physics, 2007, 101, 063509.	2.5	20
367	Effect of the compositional distribution on the photovoltaic power conversion of SiGe solar cells. Solar Energy Materials and Solar Cells, 2007, 91, 123-128.	6.2	15
368	Growth temperature dependence of lattice structures of SiGe/graded buffer structures grown on Si(110) substrates by gas-source MBE. Journal of Crystal Growth, 2007, 301-302, 343-348.	1.5	15
369	Fabrication of Ge channels with extremely high compressive strain and their magnetotransport properties. Journal of Crystal Growth, 2007, 301-302, 339-342.	1.5	1
370	Formation mechanism of parallel twins related to Si-facetted dendrite growth. Scripta Materialia, 2007, 57, 81-84.	5.2	74
371	Grazing-incidence Small-angle Scattering as a Tool for Thin Film Microstructure and Interface Analysis. Transactions of the Materials Research Society of Japan, 2007, 32, 275-280.	0.2	2
372	Single and coupled quantum wells: SiGe. Landolt-Bâˆšâˆ,rnstein - Group III Condensed Matter, 2007, , 26-49.	0.0	0
373	Strong resonant luminescence from Ge quantum dots in photonic crystal microcavity at room temperature. Applied Physics Letters, 2006, 89, 201102.	3.3	79
374	Evaluation of Strain Field Around SIC Particle in Poly-Crystalline Silicon. , 2006, , .		0
375	Spontaneous Modification of Grain Boundary Configuration and its Application for Realization of Bulk Multicrystalline Si with Electrically Inactive Grain Boundaries. , 2006, , .		0
376	Suppression of Structural Imperfection in Strained Si Thin Film by Utilizing SiGe Bulk Substrate. ECS Transactions, 2006, 3, 299-302.	0.5	0
377	ã‚·ãƒªã‚³ãƒ³ãƒãƒ«ã‚¯çµæ™¶ã®ç²’ç•Œå¶å¾¡ã«å‘ã‘ã¦. Materia Japan, 2006, 45, 720-724.	0.1	0
378	Photo-induced improvement of radiative efficiency and structural changes in GaAsN alloys. Physica Status Solidi C: Current Topics in Solid State Physics, 2006, 3, 1907-1910.	0.8	2

#	Article	IF	Citations
379	Growth of structure-controlled polycrystalline silicon ingots for solar cells by casting. Acta Materialia, 2006, 54, 3191-3197.	7.9	158
380	Directional growth method to obtain high quality polycrystalline silicon from its melt. Journal of Crystal Growth, 2006, 292, 282-285.	1.5	100
381	Influence of stacked Ge islands on the dark currentâ€“voltage characteristics and the conversion efficiency of the solar cells. Thin Solid Films, 2006, 508, 402-405.	1.8	3
382	Intermixing of Ge and Si during exposure of GeH4 on Si. Thin Solid Films, 2006, 508, 163-165.	1.8	3
383	Determination of lattice parameters of SiGe/Si(110) heterostructures. Thin Solid Films, 2006, 508, 132-135.	1.8	21
384	Strain field and related roughness formation in SiGe relaxed buffer layers. Thin Solid Films, 2006, 508, 117-119.	1.8	5
385	Development of Textured High-Quality Si Multicrystal Ingots with Same Grain Orientation and Large Grain Sizes by the New Dendritic Casting Method. , 2006, , .		1
386	High Sensitive Imaging of Atomic Arrangement of Ge Clusters Buried in a Si Crystal by X-ray Fluorescence Holography. Japanese Journal of Applied Physics, 2006, 45, 5248-5253.	1.5	1
387	Realization of Bulk Multicrystalline Silicon with Controlled Grain Boundaries by Utilizing Spontaneous Modification of Grain Boundary Configuration. Japanese Journal of Applied Physics, 2006, 45, 1734-1737.	1.5	15
388	High-Efficiency Concave and Conventional Solar Cell Integration System Using Focused Reflected Light. Japanese Journal of Applied Physics, 2006, 45, 1664-1667.	1.5	3
389	Annihilation of Acceptorâ€“Hydrogen Pairs in Si Crystals Due to Electron Irradiation. Japanese Journal of Applied Physics, 2006, 45, 9162-9166.	1.5	0
390	Unique Temperature Dependence on the Morphological Evolution of Ge on Si(100). ECS Transactions, 2006, 3, 243-244.	0.5	1
391	Development of Textured High-Quality Si and SiGe Multicrystal Ingots with Same Grain Orientation and Large Grain Sizes by the New Dendritic Casting Method. ECS Transactions, 2006, 3, 265-267.	0.5	1
392	Two-dimensional Photonic Crystal Microcavity with Germanium Self-assembled Quantum Dots. , 2006, , .		0
393	Suppression of structural imperfection in strained Si by utilizing SiGe bulk substrate. Applied Physics Letters, 2006, 88, 221912.	3.3	4
394	Magnetotransport properties of Ge channels with extremely high compressive strain. Applied Physics Letters, 2006, 89, 162103.	3.3	17
395	Growth of InGaAs and SiGe homogeneous bulk crystals which have complete miscibility in the phase diagrams. International Journal of Materials and Product Technology, 2005, 22, 185.	0.2	5
396	Effects of vicinal steps on the island growth and orientation of epitaxially grown perylene-3,4,9,10-tetracarboxylic dianhydride (PTCDA) thin film crystals on a hydrogen-terminated Si(111) substrate. Journal of Crystal Growth, 2005, 273, 594-602.	1.5	9

#	Article	IF	Citations
397	Growth and properties of SiGe multicrystals with microscopic compositional distribution and their applications for high-efficiency solar cells. Journal of Crystal Growth, 2005, 275, e455-e460.	1.5	8
398	Growth of SiGe-on-insulator and its application as a substrate for epitaxy of strained-Si layer. Journal of Crystal Growth, 2005, 275, e1203-e1207.	1.5	3
399	A simple approach to determine preferential growth orientation using multiple seed crystals with random orientations and its utilization for seed optimization to restrain polycrystallization of SiGe bulk crystal. Journal of Crystal Growth, 2005, 276, 393-400.	1.5	16
400	Structural properties of directionally grown polycrystalline SiGe for solar cells. Journal of Crystal Growth, 2005, 275, 467-473.	1.5	14
401	Growth of multicrystalline Si with controlled grain boundary configuration by the floating zone technique. Journal of Crystal Growth, 2005, 280, 419-424.	1.5	30
402	Floating zone growth of Si-rich SiGe bulk crystal using pre-synthesized SiGe feed rod with uniform composition. Journal of Crystal Growth, 2005, 284, 57-64.	1.5	26
403	Changes in elastic deformation of strained Si by microfabrication. Materials Science in Semiconductor Processing, 2005, 8, 181-185.	4.0	9
404	Observation of strain field fluctuation in SiGe-relaxed buffer layers and its influence on overgrown structures. Materials Science in Semiconductor Processing, 2005, 8, 177-180.	4.0	9
405	Crystal quality of a 6H-SiC layer grown over macrodefects by liquid-phase epitaxy: a Raman spectroscopic study. Thin Solid Films, 2005, 476, 206-209.	1.8	27
406	Strain-Field Evaluation of Strain-Relaxed Thin SiGe Layers Fabricated by Ion Implantation Method. Japanese Journal of Applied Physics, 2005, 44, L1316-L1319.	1.5	5
407	Thickness Dependence of Strain Field Distribution in SiGe Relaxed Buffer Layers. Japanese Journal of Applied Physics, 2005, 44, 8445-8447.	1.5	10
408	Analysis of the Dark-Current Density in Solar Cells Based on Multicrystalline SiGe. Japanese Journal of Applied Physics, 2005, 44, 8019-8022.	1.5	2
409	Floating Zone Growth of Si Bicrystals Using Seed Crystals with Artificially Designed Grain Boundary Configuration. Japanese Journal of Applied Physics, 2005, 44, L778-L780.	1.5	9
410	On the Origin of Improved Conversion Efficiency of Solar Cells Based on SiGe with Compositional Distribution. Japanese Journal of Applied Physics, 2005, 44, 857-860.	1.5	5
411	Influence of growth temperature on minority-carrier lifetime of Si layer grown by liquid phase epitaxy using Ga solvent. Journal of Applied Physics, 2005, 98, 073708.	2.5	1
412	Liquid Phase Epitaxial Growth of Si Layers on Si Thin Substrates from Si Pure Melts under Near-Equilibrium Conditions. Japanese Journal of Applied Physics, 2005, 44, 5092-5095.	1.5	6
413	Growth of ZnOâˆ•MgZnO quantum wells on sapphire substrates and observation of the two-dimensional confinement effect. Applied Physics Letters, 2005, 86, 032105.	3.3	112
414	Relationship between Device Performance and Grain Boundary Structural Configuration in a Solar Cell Based on Multicrystalline SiGe. Japanese Journal of Applied Physics, 2004, 43, L250-L252.	1.5	2

#	Article	IF	Citations
415	Structural and Optical Properties of ZnO Epitaxial Films Grown on Al2O3(11ar20) Substrates by Metalorganic Chemical Vapor Deposition. Japanese Journal of Applied Physics, 2004, 43, 4110-4113.	1.5	8
416	Ge composition dependence of properties of solar cells based on multicrystalline SiGe with microscopic compositional distribution. Journal of Applied Physics, 2004, 96, 1238-1241.	2.5	32
417	Fabrication of high-quality strain-relaxed thin SiGe layers on ion-implanted Si substrates. Applied Physics Letters, 2004, 85, 2514-2516.	3.3	43
418	Low-temperature growth of ZnO nanostructure networks. Journal of Applied Physics, 2004, 96, 340-343.	2.5	46
419	Effects of spacer thickness on quantum efficiency of the solar cells with embedded Ge islands in the intrinsic layer. Applied Physics Letters, 2004, 84, 2802-2804.	3.3	22
420	Formation of highly aligned ZnO tubes on sapphire (0001) substrates. Applied Physics Letters, 2004, 84, 4098-4100.	3.3	183
421	Crystal Quality Evaluation of 6H-SiC Layers Grown by Liquid Phase Epitaxy around Micropipes using Micro-Raman Scattering Spectroscopy. Materials Science Forum, 2004, 457-460, 633-636.	0.3	5
422	Successful Growth of InxGa1-xAs (x>0.18) Single Bulk Crystal Directly on GaAs Seed Crystal with Preferential Orientation. Japanese Journal of Applied Physics, 2004, 43, L907-L909.	1.5	1
423	Fabrication of solar cell with stacked Ge islands for enhanced absorption in the infrared regime. Thin Solid Films, 2004, 451-452, 604-607.	1.8	7
424	Epitaxial relation and island growth of perylene-3.4.9.10-tetracarboxylic dianhydride (PTCDA) thin film crystals on a hydrogen-terminated Si(111) substrate. Journal of Crystal Growth, 2004, 262, 196-201.	1.5	20
425	Low-temperature growth of ZnO epitaxial films by metal organic chemical vapor deposition. Applied Physics A: Materials Science and Processing, 2004, 78, 25-28.	2.3	7
426	Low-temperature growth of single-crystalline ZnO tubes on sapphire(0001) substrates. Applied Physics A: Materials Science and Processing, 2004, 79, 1711-1714.	2.3	9
427	Effects of growth temperature on the characteristics of ZnO epitaxial films deposited by metalorganic chemical vapor deposition. Thin Solid Films, 2004, 449, 12-19.	1.8	112
428	Phase diagram of growth mode for the SiGe/Si heterostructure system with misfit dislocations. Journal of Crystal Growth, 2004, 260, 372-383.	1.5	13
429	In situ observation of elementary growth steps on the surface of protein crystals by laser confocal microscopy. Journal of Crystal Growth, 2004, 262, 536-542.	1.5	98
430	In-situ observations of melt growth behavior of polycrystalline silicon. Journal of Crystal Growth, 2004, 262, 124-129.	1.5	69
431	Effects of growth temperature on the surface morphology of silicon thin films on (111) silicon monocrystalline substrate by liquid phase epitaxy. Journal of Crystal Growth, 2004, 266, 467-474.	1.5	7
432	Grain growth behaviors of polycrystalline silicon during melt growth processes. Journal of Crystal Growth, 2004, 266, 441-448.	1.5	101

#	Article	IF	Citations
433	Fabrication of SiGe-on-insulator by rapid thermal annealing of Ge on Si-on-insulator substrate. Applied Surface Science, 2004, 224, 95-98.	6.1	10
434	On the origin of strain fluctuation in strained-Si grown on SiGe-on-insulator and SiGe virtual substrates. Applied Physics Letters, 2004, 85, 1335-1337.	3.3	21
435	Pressure-Dependent ZnO Nanocrsytal Growth in a Chemical Vapor Deposition Process. Journal of Physical Chemistry B, 2004, 108, 10899-10902.	2.6	52
436	Molten metal flux growth and properties of CrSi2. Journal of Alloys and Compounds, 2004, 383, 319-321.	5.5	12
437	3D atomic imaging of SiGe system by X-ray fluorescence holography. Journal of Materials Science: Materials in Electronics, 2003, 14, 459-462.	2.2	6
438	Planarization of SiGe virtual substrates by CMP and its application to strained Si modulation-doped structures. Journal of Crystal Growth, 2003, 251, 693-696.	1.5	7
439	Growth of SiGe bulk crystals with uniform composition by utilizing feedback control system of the crystalâ€“melt interface position for precise control of the growth temperature. Journal of Crystal Growth, 2003, 250, 298-304.	1.5	30
440	Effects of high pressure on the growth kinetics of orthorhombic lysozyme crystals. Journal of Crystal Growth, 2003, 254, 188-195.	1.5	22
441	Stacked Ge islands for photovoltaic applications. Science and Technology of Advanced Materials, 2003, 4, 367-370.	6.1	13
442	Improvement in the luminescence efficiency of GaAsN alloys by photoexcitation. Physica Status Solidi C: Current Topics in Solid State Physics, 2003, 0, 2782-2784.	0.8	4
443	Optical properties of ZnO rods formed by metalorganic chemical vapor deposition. Applied Physics Letters, 2003, 83, 1635-1637.	3.3	319
444	Enhanced quantum efficiency of solar cells with self-assembled Ge dots stacked in multilayer structure. Applied Physics Letters, 2003, 83, 1258-1260.	3.3	99
445	High-Quality Crystalline Silicon Layer Grown by Liquid Phase Epitaxy Method at Low Growth Temperature. Japanese Journal of Applied Physics, 2003, 42, L217-L219.	1.5	6
446	Influence of the elastic strain on the band structure of ellipsoidal SiGe coherently embedded in the Si matrix. Journal of Applied Physics, 2003, 94, 916-920.	2.5	19
447	In-plane strain fluctuation in strained-Si/SiGe heterostructures. Applied Physics Letters, 2003, 83, 4339-4341.	3.3	61
448	Epitaxial Growth and Polarity of ZnO Films on Sapphire (0001) Substrates by Low-Pressure Metal Organic Chemical Vapor Deposition. Japanese Journal of Applied Physics, 2003, 42, 2291-2295.	1.5	34
449	Fabrication of SiGe-on-Insulator through Thermal Diffusion of Ge on Si-on-Insulator Substrate. Japanese Journal of Applied Physics, 2003, 42, L232-L234.	1.5	8
450	In-Plane Orientation and Polarity of ZnO Epitaxial Films on As-Polished Sapphire (Î±-Al2O3) (0001) Substrates Grown by Metal Organic Chemical Vapor Deposition. Japanese Journal of Applied Physics, 2003, 42, L264-L266.	1.5	14

#	Article	IF	Citations
451	High-Temperature Solution Growth and Characterization of Chromium Disilicide. Japanese Journal of Applied Physics, 2003, 42, 7292-7293.	1.5	3
452	Strain distribution of Si thin film grown on multicrystalline-SiGe with microscopic compositional distribution. Journal of Applied Physics, 2002, 92, 7098-7101.	2.5	2
453	Control of Macroscopic Absorption Coefficient of Multicrystalline SiGe by Microscopic Compositional Distribution. Japanese Journal of Applied Physics, 2002, 41, L37-L39.	1.5	10
454	Evidence of the Presence of Built-in Strain in Multicrystalline SiGe with Large Compositional Distribution. Japanese Journal of Applied Physics, 2002, 41, 4462-4465.	1.5	9
455	Preparation of a TiO₂ Film Coated Si Device for Photo-Decomposition of Water by CVD Method Using Ti(OPrⁱ)₄. Materials Transactions, 2002, 43, 1533-1536.	1.2	7
456	PHONON REPLICA OF FREE EXCITONS IN ZnO EPITAXIAL FILMS. Nonlinear Optics, Quantum Optics, 2002, 29, 621-627.	0.2	4
457	Raman scattering and x-ray absorption studies of Geâ€“Si nanocrystallization. Applied Physics Letters, 2002, 80, 488-490.	3.3	26
458	Evaluation of the diffusion coefficients in liquid GaGe binary alloys using a novel method based on Fickâ€™s first law. Journal of Non-Crystalline Solids, 2002, 312-314, 196-202.	3.1	4
459	Strain-driven alloying: effect on sizes, shape and photoluminescence of GeSi/Si(001) self-assembled islands. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2002, 89, 62-65.	3.5	18
460	Fabrication of SiGe bulk crystals with uniform composition as substrates for Si-based heterostructures. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2002, 89, 364-367.	3.5	5
461	Melt growth of multicrystalline SiGe with large compositional distribution for new solar cell applications. Solar Energy Materials and Solar Cells, 2002, 72, 93-100.	6.2	17
462	In situ observations of crystal growth behavior of silicon melt. Journal of Crystal Growth, 2002, 243, 275-282.	1.5	71
463	Growth and properties of SiGe multicrystals with microscopic compositional distribution for high-efficiency solar cells. Solar Energy Materials and Solar Cells, 2002, 73, 305-320.	6.2	16
464	In situ observation of the Marangoni convection in a NaCl aqueous solutions under microgravity. Journal of Crystal Growth, 2002, 234, 516-522.	1.5	6
465	In-situ monitoring system of the position and temperature at the crystalâ€“solution interface. Journal of Crystal Growth, 2002, 236, 125-131.	1.5	14
466	Compositional variation in Si-rich SiGe single crystals grown by multi-component zone melting method using Si seed and source crystals. Journal of Crystal Growth, 2002, 240, 373-381.	1.5	35
467	New method for measurement of interdiffusion coefficient in high temperature solutions based on Fick's first law. Journal of Crystal Growth, 2002, 241, 387-394.	1.5	18
468	Simultaneous in situ measurement of solute and temperature distributions in the alloy solutions. Journal of Crystal Growth, 2002, 242, 313-320.	1.5	7

#	Article	IF	Citations
469	Observation of negatively charged excitons and excited states of multi-excitons in quantum dots embedded in modulation doping structures. Physica E: Low-Dimensional Systems and Nanostructures, 2001, 11, 68-71.	2.7	4
470	Modification of the growth mode of Ge on Si(100) in the presence of buried Ge islands. Journal of Crystal Growth, 2001, 227-228, 782-785.	1.5	1
471	Growth of SiGe bulk crystal with uniform composition by directly controlling the growth temperature at the crystalâ€“melt interface using in situ monitoring system. Journal of Crystal Growth, 2001, 224, 204-211.	1.5	49
472	Growth of SixGe1-x($x allingdotseq 0.15$) Bulk Crystal with Uniform Composition Utilizingin situMonitoring of the Crystal-solution Interface. Japanese Journal of Applied Physics, 2001, 40, 4141-4144.	1.5	11
473	Molecular beam epitaxy of GaAs on nearly lattice-matched SiGe substrates grown by the multicomponent zone-melting method. Semiconductor Science and Technology, 2001, 16, 699-703.	2.0	7
474	Physical model for the evaluation of solidâ€“liquid interfacial tension in silicon. Journal of Applied Physics, 2001, 90, 750-755.	2.5	19
475	Fabrication of strain-balanced Si/Si1â^'xGex multiple quantum wells on Si1â^'yGey virtual substrates and their optical properties. Applied Physics Letters, 2001, 79, 344-346.	3.3	7
476	Effect of Si diffusion on growth of GeSi self-assembled islands. Springer Proceedings in Physics, 2001, , 377-378.	0.2	0
477	Phase diagram calculation for epitaxial growth of GaInAs on InP considering the surface, interfacial and strain energies. Journal of Crystal Growth, 2000, 220, 413-424.	1.5	12
478	Drastic modification of the growth mode of Ge quantum dots on Si by using boron adlayer. Thin Solid Films, 2000, 369, 84-87.	1.8	23
479	Optical investigation of modified Stranskiâ€“Krastanov growth mode in the stacking of self-assembled Ge islands. Thin Solid Films, 2000, 369, 108-111.	1.8	22
480	Formation of relaxed SiGe films on Si by selective epitaxial growth. Thin Solid Films, 2000, 369, 126-129.	1.8	16
481	Growth and characterization of 70 Ge n / 74 Ge n isotope superlattices. Thin Solid Films, 2000, 369, 405-408.	1.8	19
482	Correlation between electronic states and optical properties in indirect GaAsP/GaP quantum wells with insertion of an ultrathin AlP layer. Physica E: Low-Dimensional Systems and Nanostructures, 2000, 8, 323-327.	2.7	3
483	In SituMeasurement of Composition in High-Temperature Solutions by X-Ray Fluorescence Spectrometry. Japanese Journal of Applied Physics, 2000, 39, 5981-5982.	1.5	6
484	SiGe bulk crystal as a lattice-matched substrate to GaAs for solar cell applications. Applied Physics Letters, 2000, 77, 3565-3567.	3.3	15
485	Drastic increase of the density of Ge islands by capping with a thin Si layer. Applied Physics Letters, 2000, 77, 217-219.	3.3	8
486	Modification of the growth mode of Ge on Si by buried Ge islands. Applied Physics Letters, 2000, 76, 3723-3725.	3.3	19

#	Article	IF	Citations
487	Selective epitaxial growth of dot structures on patterned Si substrates by gas source molecular beam epitaxy. Semiconductor Science and Technology, 1999, 14, 257-265.	2.0	27
488	Magnetophotoluminescence spectroscopy of AlGaP-based neighboring confinement structures. Physical Review B, 1999, 60, 1879-1883.	3.2	4
489	Effect of the insertion of an ultrathin AlP layer on the optical properties of GaAsP/GaP quantum wells. Physical Review B, 1999, 60, 13735-13739.	3.2	5
490	Optical characterization of strain-induced structural modification in SiGe-based heterostructures. Journal of Applied Physics, 1999, 85, 2363-2366.	2.5	15
491	Study of a Pure-Ge/Si Short-Period Superlattice by X-Ray Double Crystal Diffraction. Journal of Materials Synthesis and Processing, 1999, 7, 205-207.	0.3	0
492	Gas source molecular beam epitaxy grown strained-Si films on step-graded relaxed Si1â^'xGex for MOS applications. Journal of Electronic Materials, 1999, 28, 98-104.	2.2	4
493	Enhanced no-phonon transition in indirect GaAsP/GaP quantum wells by insertion of monolayer AlP for electron localization. Journal of Crystal Growth, 1998, 188, 323-327.	1.5	2
494	Exciton diffusion dynamics in quantum nanostructures on V-groove patterned substrates. Superlattices and Microstructures, 1998, 23, 395-400.	3.1	0
495	Effect of tensile strain on optical properties of AlGaP-based neighboring confinement structure. Superlattices and Microstructures, 1998, 23, 97-102.	3.1	1
496	Control of island formation using overgrowth technique on cleaved edges of strained multiple quantum wells and selective epitaxy on patterned substrates. Physica E: Low-Dimensional Systems and Nanostructures, 1998, 2, 137-141.	2.7	1
497	Temperature dependence of microscopic photoluminescence spectra of quantum dots and quantum wells. Physica E: Low-Dimensional Systems and Nanostructures, 1998, 2, 573-577.	2.7	47
498	In-plane potential modulation in tensilely strained AlGaP-based neighboring confinement structure. Physica E: Low-Dimensional Systems and Nanostructures, 1998, 2, 883-886.	2.7	2
499	Magneto-photoluminescence spectra of GaP/AlP short-period superlattices in high magnetic fields and uniaxial pressures. Physica B: Condensed Matter, 1998, 249-251, 909-913.	2.7	6
500	Electrical properties of N2O/NH3 plasma grown oxynitride on strained-Si. IEEE Electron Device Letters, 1998, 19, 273-275.	3.9	7
501	Photoluminescence from pure-Ge/pure-Si neighboring confinement structure. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1998, 16, 1710.	1.6	0
502	Photoluminescence and Raman scattering of pure germanium/silicon short period superlattice. Acta Physica Sinica (overseas Edition), 1998, 7, 608-612.	0.1	0
503	New strain-relieving microstructure in pure-Ge/Si short-period superlattices. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1998, 16, 1595.	1.6	3
504	Epitaxial growth and photoluminescence of Si/pure-Ge/Si quantum structures on Si(311) substrates. Semiconductor Science and Technology, 1998, 13, 1277-1283.	2.0	2

#	Article	IF	Citations
505	Wavy interface morphologies in strained multilayers on vicinal Si(111) substrates. Journal of Physics Condensed Matter, 1998, 10, 8643-8652.	1.8	6
506	Control of Ge dots in dimension and position by selective epitaxial growth and their optical properties. Applied Physics Letters, 1998, 72, 1617-1619.	3.3	128
507	SiGe Quantum Structures. Nanoscience and Technology, 1998, , 264-271.	1.5	0
508	Interfacial roughness of multilayer structures on Si(111) probed by x-ray scattering. Journal of Physics Condensed Matter, 1997, 9, 4521-4533.	1.8	5
509	Spectroscopic study of Si-based quantum wells with neighbouring confinement structure. Semiconductor Science and Technology, 1997, 12, 1596-1602.	2.0	6
510	Effects of tensile strain on the optical properties of an AlGaP-based neighbouring confinement structure. Semiconductor Science and Technology, 1997, 12, 881-887.	2.0	5
511	Oxidation of strained Si in a microwave electron cyclotron resonance plasma. Applied Physics Letters, 1997, 70, 217-219.	3.3	14
512	Photoluminescence study of the optical properties of SiGe quantum wells on separation by implanted oxygen substrates. Journal of Applied Physics, 1997, 81, 3484-3489.	2.5	2
513	Precise control of island formation using overgrowth technique on cleaved edges of strained multiple quantum wells. Applied Physics Letters, 1997, 70, 2981-2983.	3.3	12
514	Electrical properties of oxides grown on strained Si using microwave N2O plasma. Applied Physics Letters, 1997, 70, 66-68.	3.3	16
515	Anomalous luminescence peak shift of SiGe/Si quantum well induced by self-assembled Ge islands. Applied Physics Letters, 1997, 70, 295-297.	3.3	13
516	Optical investigation of growth mode of Ge thin films on Si(110) substrates. Applied Physics Letters, 1997, 71, 785-787.	3.3	13
517	Anomalous photoluminescence of pure-Ge/Si type-II coupled quantum wells (II-CQWs). Thin Solid Films, 1997, 294, 336-339.	1.8	3
518	Luminescence study on Ge islands as stressors on quantum well. Journal of Crystal Growth, 1997, 175-176, 519-523.	1.5	3
519	Physics and Control of Si/Ge Heterointerfaces. Materials Research Society Symposia Proceedings, 1996, 448, 125.	0.1	0
520	Exciton diffusion dynamics in quantum wells on a V-groove patterned Si substrate. Solid-State Electronics, 1996, 40, 733-736.	1.4	0
521	Formation and optical properties of SiGe/Si quantum structures. Applied Surface Science, 1996, 102, 263-271.	6.1	18
522	Timeâ€resolved photoluminescence study on AlxGa1â^'xAs spontaneous vertical quantum well structures. Applied Physics Letters, 1996, 68, 3221-3223.	3.3	1

#	Article	IF	Citations
523	Observation of lateral confinement effect in Ge quantum wires selfâ€aligned at step edges on Si(100). Applied Physics Letters, 1996, 68, 1847-1849.	3.3	40
524	Ultrashort lifetime photocarriers in Ge thin films. Applied Physics Letters, 1996, 68, 3419-3421.	3.3	20
525	Role of heterointerface on enhancement of noâ€phonon luminescence in Siâ€based neighboring confinement structure. Applied Physics Letters, 1996, 68, 2340-2342.	3.3	26
526	Rectangular AlGaAs/AlAs Quantum Wires Using Spontaneous Vertical Quantum Wells. Japanese Journal of Applied Physics, 1996, 35, 1214-1216.	1.5	5
527	Improved luminescence quality with an asymmetric confinement potential in Si-based type-II quantum wells grown on a graded SiGe relaxed buffer. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1996, 14, 2387.	1.6	8
528	Anomalous spectral shift of photoluminescence from MBE-grown strained Si1â^'xGex/Si quantum wells mediated by atomic hydrogen. , 1996, , 36-39.		0
529	Intense photoluminescence from Si-based quantum well structures with neighboring confinement structure. , 1996, , 27-30.		0
530	Photoluminescence investigation on growth mode changeover of Ge on Si(100). , 1996, , 265-269.		0
531	Photoluminescence investigation on growth mode changeover of Ge on Si(100). Journal of Crystal Growth, 1995, 157, 265-269.	1.5	45
532	Intense photoluminescence from Si-based quantum well structures with neighboring confinement structure. Journal of Crystal Growth, 1995, 157, 27-30.	1.5	6
533	Anomalous spectral shift of photoluminescence from MBE-grown strained quantum wells mediated by atomic hydrogen. Journal of Crystal Growth, 1995, 157, 36-39.	1.5	3
534	Field-driven blue shift of excitonic photoluminescence in Siî—¸Ge quantum wells and superlattices. Journal of Crystal Growth, 1995, 157, 40-44.	1.5	8
535	Crucial role of Si buffer layer quality in the photoluminescence efficiency of strained Si1â^'xGex/Si quantum wells. Journal of Crystal Growth, 1995, 150, 1033-1037.	1.5	1
536	Strain-induced lateral band gap modulation in Si1â^'xGex/Si quantum well and quantum wire structures. Journal of Crystal Growth, 1995, 150, 1065-1069.	1.5	7
537	Cathodoluminescence investigation of SiGe quantum wires fabricated on V-groove patterned Si substrates. Journal of Crystal Growth, 1995, 150, 1070-1073.	1.5	10
538	Enhancement of radiative recombination in Siâ€based quantum wells with neighboring confinement structure. Applied Physics Letters, 1995, 67, 524-526.	3.3	46
539	Characterization of SiGe quantum wire structures by cathodoluminescence imaging and spectroscopy. Applied Physics Letters, 1995, 67, 1709-1711.	3.3	4
540	Dynamics of exciton diffusion in SiGe quantum wells on assV-groove patterned Si substrate. Physical Review B, 1995, 52, 5132-5135.	3.2	6

#	Article	IF	Citations
541	Island formation during growth of Ge on Si(100): A study using photoluminescence spectroscopy. Applied Physics Letters, 1995, 66, 3024-3026.	3.3	263
542	Formation and Properties of SiGe/Si Quantum Wire Structures. , 1995, , 151-160.		1
543	Optical Detection of Interdiffusion in StrainedSi1-xGex/SiQuantum Well Structures. Japanese Journal of Applied Physics, 1994, 33, 2344-2347.	1.5	12
544	Photoluminescence ofSi1-xGex/SiQuantum Wells with Abrupt Interfaces Formed by Segregant-Assisted Growth. Japanese Journal of Applied Physics, 1994, 33, 2304-2306.	1.5	2
545	Optical anisotropy in wireâ€geometry SiGe layers grown by gasâ€source selective epitaxial growth technique. Applied Physics Letters, 1994, 64, 1126-1128.	3.3	74
546	Abrupt Si/Ge interface formation using atomic hydrogen in Si molecular beam epitaxy. Applied Physics Letters, 1994, 65, 2975-2977.	3.3	54
547	Fabrication of SiGe/Si quantum wire structures on a V-groove patterned Si substrate by gas-source Si molecular beam epitaxy. Solid-State Electronics, 1994, 37, 539-541.	1.4	14
548	Band-edge photoluminescence of SiGe/strained-Si/SiGe type-II quantum wells on Si(100). Solid-State Electronics, 1994, 37, 933-936.	1.4	8
549	Gas-source molecular beam epitaxy and luminescence characterization of strained Si1â^'xGex/Si quantum wells. Journal of Crystal Growth, 1994, 136, 315-321.	1.5	46
550	A Si1â^'xGex/Si single quantum well p-i-n structure grown by solid-source and gas source â€œhybridâ€•Si molecular beam epitaxy. Journal of Crystal Growth, 1994, 136, 355-360.	1.5	1
551	Photoluminescence of Si/SiGe/Si quantum wells on separation by oxygen implantation substrate. Applied Physics Letters, 1994, 64, 2373-2375.	3.3	5
552	Is low temperature growth the solution to abrupt Siâ§Si1-xGex interface formation?. Journal of Crystal Growth, 1993, 127, 401-405.	1.5	20
553	Intense photoluminescence from strained Si1-xGexâ§Si quantum well structures. Journal of Crystal Growth, 1993, 127, 489-493.	1.5	3
554	Observation of electroluminescence above room temperature in strained p-type Si0.65Ge0.35/Si(111) multiple quantum wells. Journal of Crystal Growth, 1993, 127, 1083-1087.	1.5	6
555	Self-modulating Sb incorporation in Si/SiGe superlattices during molecular beam epitaxial growth. Surface Science, 1993, 295, 335-339.	1.9	9
556	Dislocation glide motion in heteroepitaxial thin films of Si_{1â^'x}Ge_x/Si(100). Philosophical Magazine Letters, 1993, 67, 165-171.	1.2	49
557	Luminescence from Strained Si1-xGex/Si Quantum Wells Grown by Si Molecular Beam Epitaxy. Japanese Journal of Applied Physics, 1993, 32, 1502-1507.	1.5	38
558	Band-Edge Photoluminescence of SiGe/Strained-Si/SiGe Type-II Quantum Wells on Si(100). Japanese Journal of Applied Physics, 1993, 32, L1391-L1393.	1.5	6

#	Article	IF	Citations
559	Hybrid Si molecular beam epitaxial regrowth for a strained Si1â^'xGex/Si singleâ€quantumâ€well electroluminescent device. Applied Physics Letters, 1993, 63, 2414-2416.	3.3	13
560	Bandâ€edge photoluminescence of SiGe/strainedâ€Si/SiGe typeâ€II quantum wells on Si(100). Applied Physics Letters, 1993, 63, 3509-3511.	3.3	35
561	Luminescence study on interdiffusion in strained Si1â^'xGex/Si single quantum wells grown by molecular beam epitaxy. Applied Physics Letters, 1993, 63, 1651-1653.	3.3	53
562	Realization of crescentâ€shaped SiGe quantum wire structures on a Vâ€groove patterned Si substrate by gasâ€source Si molecular beam epitaxy. Applied Physics Letters, 1993, 63, 2789-2791.	3.3	53
563	Highâ€temperature operation of strained Si0.65Ge0.35/Si(111)pâ€type multipleâ€quantumâ€well lightâ€emitting diode grown by solid source Si molecularâ€beam epitaxy. Applied Physics Letters, 1993, 63, 967-969.	3.3	33
564	Abrupt compositional transition in luminescent Si1â^'xGex/Si quantum well structures fabricated by segregant assisted growth using Sb adlayer. Applied Physics Letters, 1993, 63, 388-390.	3.3	29
565	Self-Modulating Incorporation of Sb in Si/SiGe Superlattices during Molecular Beam Epitaxial Growth. Materials Science Forum, 1993, 117-118, 159-164.	0.3	0
566	Quantum Size Effect of Excitonic Band-Edge Luminescence in Strained Si1-xGex/Si Single Quantum Well Structures Grown by Gas-Source Si Molecular Beam Epitaxy. Japanese Journal of Applied Physics, 1992, 31, L1319-L1321.	1.5	29
567	Photogeneration and Transport of Carriers in Strained Si1-xGex/Si Quantum Well Structures. Japanese Journal of Applied Physics, 1992, 31, L1525-L1528.	1.5	10
568	Band-Edge Luminescence of Strained SixGe1-x/Si Single Quantum Well Structures Grown on Si(111) by Si Molecular Beam Epitaxy. Japanese Journal of Applied Physics, 1992, 31, L1018-L1020.	1.5	10
569	Electroluminescence from Strained SiGe/Si Quantum Well Structures Grown by Solid Source Si Molecular Beam Epitaxy. Japanese Journal of Applied Physics, 1992, 31, L1015-L1017.	1.5	32
570	Observation of deepâ€levelâ€free band edge luminescence and quantum confinement in strained Si1â^'xGex/Si single quantum well structures grown by solid source Si molecular beam epitaxy. Applied Physics Letters, 1992, 61, 1706-1708.	3.3	47
571	Systematic blue shift of exciton luminescence in strained Si1 â^'s xGex/Si quantum well structures grown by gas source silicon molecular beam epitaxy. Thin Solid Films, 1992, 222, 1-4.	1.8	17
572	Excitonic Band Edge Luminescence in Strained Si1-xGex/Si Quantum Well Structures Grown by Gas-Source Si Molecular Beam Epitaxy. , 1992, , .		0
573	â€œSolid Source" Molecular Beam Epitaxial Growth of Highly Luminescent Si1-xGex/Si Quantum Well Structures. , 1992, , .		0
574	Planarization of SiGe virtual substrates by CMP and its application to strained Si modulation-doped structures. , 0, , .		0
575	Grain growth of polycrystalline Si thin film for solar cells and its effect on crystal properties. , 0, , .		0
576	Si/multicrystalline-SiGe heterostructure as a candidate for solar cells with high conversion efficiency. , 0, , .		0

#	Article	IF	Citations
577	Growth of ZnO epitaxial films by metal organic chemical vapor deposition at various temperatures. , 0, , .		0
578	Fabrication of p-i-n Si/sub 0.5/Ge/sub 0.5/ photodetectors on SiGe-on-insulator substrates. , 0, , .		0
579	New solar cells using Ge dots embedded in Si PIN structures. , 0, , .		0
580	Investigation of crystal growth behavior of silicon melt for growing high quality polycrystalline silicon by cast method. , 0, , .		0
581	Development of Thin SiGe Relaxed Layers with High-Ge Composition by Ion Implantation Method and Application to Strained Ge Channels. Applied Physics Express, 0, 1, 081401.	2.4	7
582	Introduction of Uniaxial Strain into Si/Ge Heterostructures by Selective Ion Implantation. Applied Physics Express, 0, 1, 121401.	2.4	13
583	Photoresponse Properties of Polycrystalline BaSi₂Films Grown on SiO₂Substrates Using (111)-Oriented Si Layers by an Aluminum-Induced Crystallization Method. Applied Physics Express, 0, 2, 051601.	2.4	55
584	Effects of Annealing Process on the Structure of Mn-Doped BiFeO₃ Thin Films. Key Engineering Materials, 0, 566, 155-158.	0.4	0
585	Realization of crystalline BaSi2 thin films by vacuum evaporation on (111)-oriented Si layers fabricated by aluminum induced crystallization. , 0, , .		2
586	Preferred orientation of BaSi2 thin films fabricated by thermal evaporation. , 0, , .		2
587	Estimation of Crystal Orientation of Grains on Polycrystalline Silicon Substrate by Recurrent Neural Network. IEEJ Transactions on Electrical and Electronic Engineering, 0, , .	1.4	2